4 Mbit LPC Flash
SST49LF040

Advance Information

FEATURES:

- **LPC Interface Flash**
  - SST49LF040: 512K x8 (4 Mbit)
- **Conforms to Intel LPC Interface Specification 1.0**
- **Flexible Erase Capability**
  - Uniform 4 KByte sectors
  - Uniform 64 KByte overlay blocks
  - 64 KByte Top boot block protection
  - Chip-Erase for PP Mode Only
- **Single 3.0-3.6V Read and Write Operations**
- **Superior Reliability**
  - Endurance: 100,000 Cycles (typical)
  - Greater than 100 years Data Retention
- **Low Power Consumption**
  - Active Read Current: 6 mA (typical)
  - Standby Current: 10 µA (typical)
- **Fast Sector-Erase/Byte-Program Operation**
  - Sector-Erase Time: 18 ms (typical)
  - Block-Erase Time: 18 ms (typical)
  - Chip-Erase Time: 70 ms (typical)
  - Byte-Program Time: 14 µs (typical)
  - Chip Rewrite Time: 8 seconds (typical)
  - Single-pulse Program or Erase
  - Internal timing generation
- **Two Operational Modes**
  - Low Pin Count (LPC) Interface mode for in-system operation
  - Parallel Programming (PP) mode for fast production programming
- **LPC Interface Mode**
  - 5-signal communication interface supporting byte Read and Write
  - 33 MHz clock frequency operation
  - WP# and TBL# pins provide hardware write protect for entire chip and/or top boot block
  - Standard SDP Command Set
  - Data# Polling and Toggle Bit for End-of-Write detection
  - 5 GPI pins for system design flexibility
  - ID pins for multi-chip selection
  - Decode both top and bottom regions of the system memory map
- **Parallel Programming (PP) Mode**
  - 11-pin multiplexed address and 8-pin data I/O interface
  - Supports fast programming In-System on programmer equipment
- **CMOS and PCI I/O Compatibility**
- **Packages Available**
  - 32-lead PLCC
  - 32-lead TSOP (8mm x 14mm)

PRODUCT DESCRIPTION

The SST49LF040 flash memory devices are designed to interface with the LPC bus for PC and Internet Appliance application in compliance with Intel Low Pin Count (LPC) Interface Specification 1.0. Two interface modes are supported by the SST49LF040: LPC mode for In-System operation and Parallel Programming (PP) mode to interface with programmer equipment.

The SST49LF040 flash memory devices are manufactured with SST's proprietary, high performance SuperFlash Technology. The split-gate cell design and thick oxide tunneling injector attain better reliability and manufacturability compared with alternate approaches. The SST49LF040 device significantly improves performance and reliability, while lowering power consumption. The SST49LF040 device writes (Program or Erase) with a single 3.0-3.6V power supply. It uses less energy during Erase and Program than alternative flash memory technologies. The total energy consumed is a function of the applied voltage, current and time of application. Since for any give voltage range, the SuperFlash technology uses less current to program and has a shorter erase time, the total energy consumed during any Erase or Program operation is less than alternative flash memory technologies. The SST49LF040 product provides a maximum Byte-Program time of 20 µsec. The entire memory can be erased and programmed byte-by-byte typically in 8 seconds when using status detection features such as Toggle Bit or Data# Polling to indicate the completion of Program operation. The SuperFlash technology provides fixed Erase and Program time, independent of the number of Erase/Program cycles that have performed. Therefore the system software or hardware does not have to be calibrated or correlated to the cumulative number of erase cycles as is necessary with alternative flash memory technologies, whose Erase and Program time increase with accumulated Erase/Program cycles.

To meet high density, surface mount requirements, the SST49LF040 device is offered in 32-lead TSOP and 32-lead PLCC packages. See Figures 2 and 3 for pin assignments and Table 1 for pin descriptions.

Advance Information

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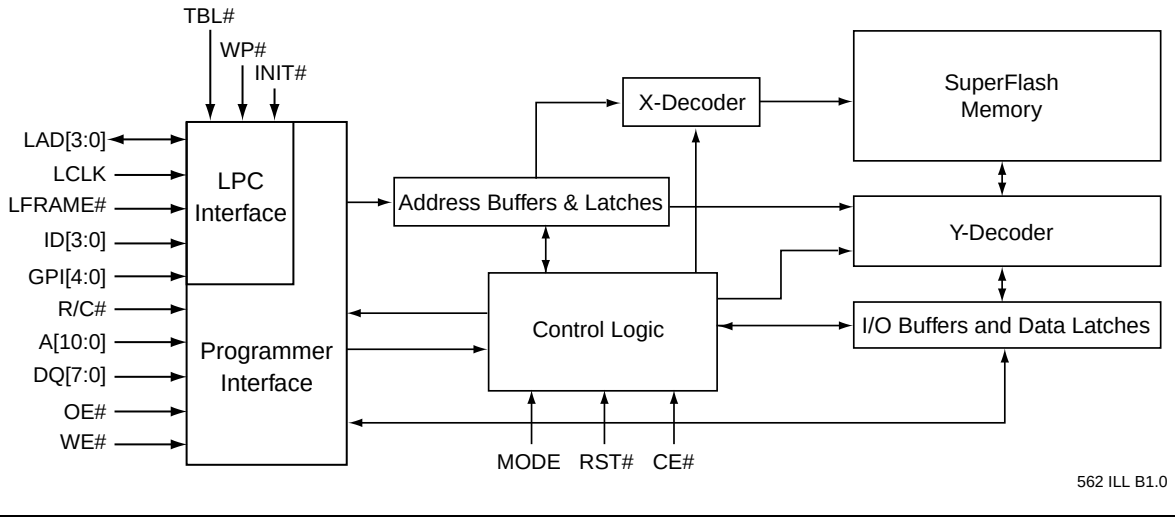
FUNCTIONAL BLOCKS



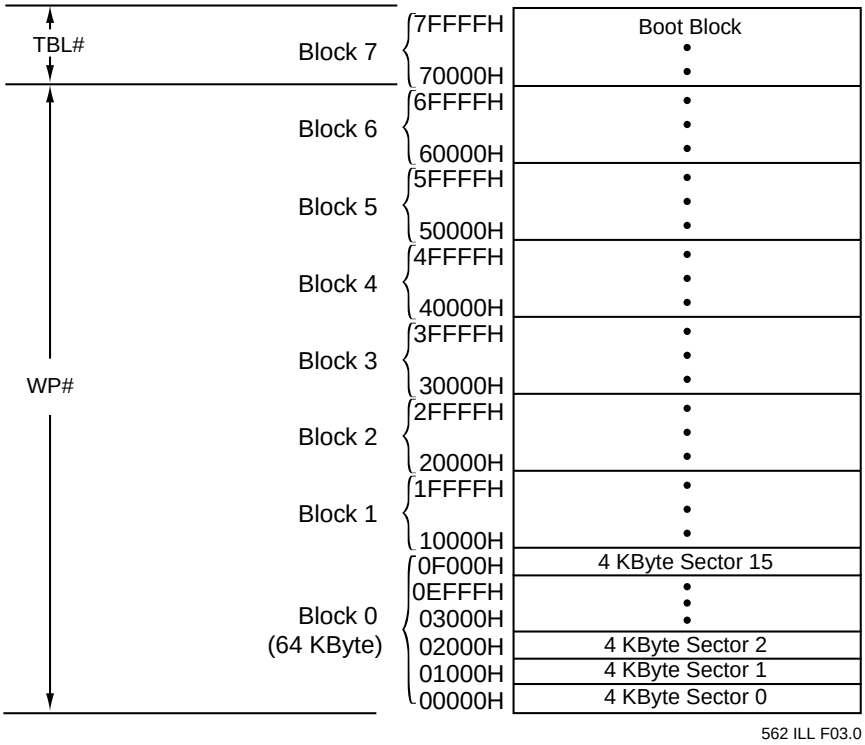
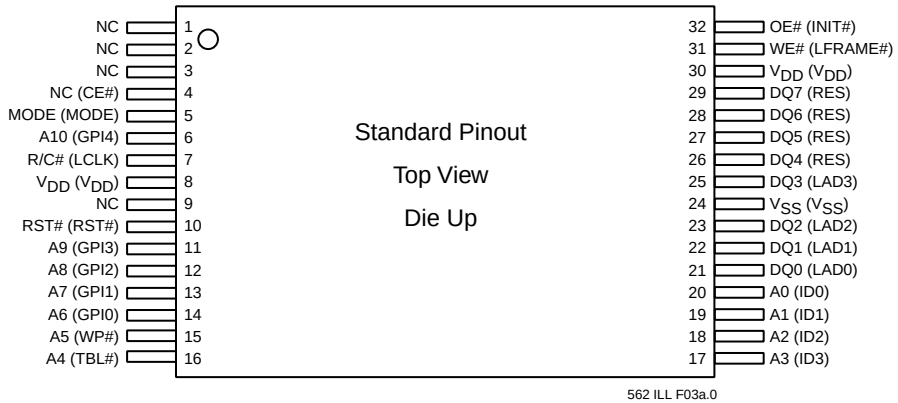


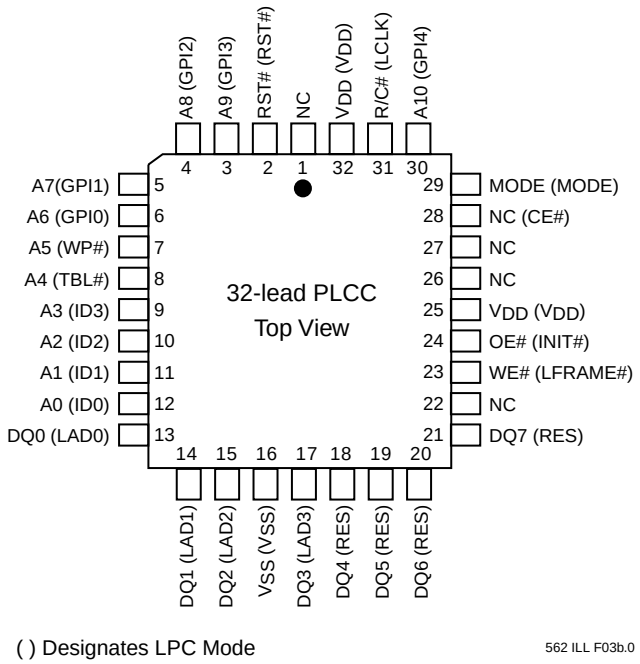
FIGURE 1: DEVICE MEMORY MAP FOR SST49LF040

PIN DESCRIPTION



( ) Designates LPC Mode

FIGURE 2: PIN ASSIGNMENTS FOR 32-LEAD TSOP (8MM X 14MM)



( ) Designates LPC Mode

FIGURE 3: PIN ASSIGNMENTS FOR 32-LEAD PLCC

TABLE 1: PIN DESCRIPTION

Symbol	Pin Name	Type[1]	Interface		Functions
			PP	LPC	
A_{10}-A_0	Address	I	X		Inputs for low-order addresses during Read and Write operations. Addresses are internally latched during a Write cycle. For the programming interface, these addresses are latched by R/C# and share the same pins as the high-order address inputs.
DQ_7-DQ_0	Data	I/O	X		To output data during Read cycles and receive input data during Write cycles. Data is internally latched during a Write cycle. The outputs are in tri-state when OE# is high.
OE#	Output Enable	I	X		To gate the data output buffers.
WE#	Write Enable	I	X		To control the Write operations.
MODE	Interface Mode Select	I	X	X	This pin determines which interface is operational. When held high, programmer mode is enabled and when held low, LPC mode is enabled. This pin must be setup at power-up or before return from reset and not change during device operation. This pin must be held high (V_{IH}) for PP mode and low (V_{IL}) for LPC mode.
INIT#	Initialize	I		X	This is the second reset pin for in-system use. This pin is internally combined with the RST# pin; If this pin or RST# pin is driven low, identical operation is exhibited.
ID[3:0] or ID[3:1]	Identification Inputs	I		X	These four pins are part of the mechanism that allows multiple parts to be attached to the same bus. These pins are internally pulled-down with a resistor between 20-100 KΩ
GPI[4:0]	General Purpose Inputs	I		X	These individual inputs can be used for additional board flexibility. The state of these pins can be read through LPC registers. These inputs should be at their desired state before the start of the PCI clock cycle during which the read is attempted, and should remain in place until the end of the Read cycle. Unused GPI pins must not be floated.
TBL#	Top Block Lock	I		X	When low, prevents programming to the boot block sectors at top of memory. When TBL# is high it disables hardware write protection for the top block sectors. This pin cannot be left unconnected.
LAD[3:0]	Address and Data	I/O		X	To provide LPC control signals, as well as addresses and Command Inputs/Outputs data.
LCLK	Clock	I		X	To provide a clock input to the control unit
LFRAME#	Frame	I		X	To indicate start of a data transfer operation; also used to abort an LPC cycle in progress.
RST#	Reset	I	X	X	To reset the operation of the device
WP#	Write Protect	I		X	When low, prevents programming to all but the highest addressable blocks. When WP# is high it disables hardware write protection for these blocks. This pin cannot be left unconnected.
R/C#	Row/Column Select	I	X		Select for the Programming interface, this pin determines whether the address pins are pointing to the row addresses, or to the column addresses.
RES	Reserved			X	These pins must be left unconnected.
V_{DD}	Power Supply	PWR	X	X	To provide power supply (3.0-3.6V)
V_{SS}	Ground	PWR	X	X	Circuit ground (0V reference)
CE#	Chip Enable	I		X	This signal must be asserted to select the device. When CE# is low, the device is enabled. CE# must remain low during internal Write (Program or Erase) operations. When CE# is high, the device is placed in low power Standby mode.
NC	No Connection	I	X	X	Unconnected pins.

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1. I=Input, O=Output

MODE SELECTION

The SST49LF040 flash memory devices can operate in two distinct interface modes: the LPC mode and the Parallel Programming (PP) mode. The mode pin is used to set the interface mode selection. If the mode pin is set to logic High, the device is in PP mode; while if the mode pin is set Low, the device is in the LPC mode. The mode selection pin must be configured prior to device operation. The mode pin is internally pulled down if the pin is left unconnected. In LPC mode, the device is configured to its host using standard LPC interface protocol. Communication between Host and the SST49LF040 occurs via the 4-bit I/O communication signals, LAD [3:0] and LFRAME#. In PP mode, the device is programmed via an 11-bit address and an 8-bit data I/O parallel signals. The address inputs are multiplexed in row and column selected by control signal R/C# pin. The row addresses are mapped to the higher internal addresses, and the column addresses are mapped to the lower internal addresses. See Figure 1, the Device Memory Map, for address assignments.

LPC MODE

CE#

The CE# pin, enables and disables the SST49LF040, controlling Read and Write access of the device. To enable the SST49LF040, the CE# pin must be driven low one clock cycle prior to LFRAME# being driven low. CE# must remain active low during internal Write (Erase or Program) operations. The device will enter the Standby mode when internal Write operations are completed and CE# is high.

LFRAME#

The LFRAME# signifies the start of a frame or the termination of a broken frame. Asserting LFRAME# for one or more clock cycle and driving a valid START value on LAD[3:0] will initiate device operation. The device will enter the Standby mode when internal operations are completed and LFRAME# is high.

Device Memory Hardware Write Protection

The Top Boot Lock (TBL#) and Write Protect (WP#) pins are provided for hardware write protection of device memory in the SST49LF040. The TBL# pin is used to write protect 16 boot sectors (64 KByte) at the highest memory address range for the SST49LF040. WP# pin write protects the remaining sectors in the flash memory.

An active low signal at the TBL# pin prevents Program and Erase operations of the top boot sectors. When TBL# pin is held high, the write protection of the top boot sectors is disabled. The WP# pin serves the same function for the remaining sectors of the device memory. The TBL# and WP# pins write protection functions operate independently of one another.

Both TBL# and WP# pins must be set to their required protection states prior to starting a Program or Erase operation. A logic level change occurring at the TBL# or WP# pin during a Program or Erase operation could cause unpredictable results.

Reset

A V_{IL} on INIT# or RST# pin initiates a device reset. INIT# and RST# pins have the same function internally. It is required to drive INIT# or RST# pins low during a system reset to ensure proper CPU initialization. During a Read operation, driving INIT# or RST# pins low deselects the device and places the output drivers, LAD[3:0], in a high-impedance state. The reset signal must be held low for a minimal duration of time T_{RSTP}. A reset latency will occur if a reset procedure is performed during a Program or Erase operation. See Table 14, Reset Timing Parameters, for more information. A device reset during an active Program or Erase will abort the operation and memory contents may become invalid due to data being altered or corrupted from an incomplete Erase or Program operation.

Device Operation

The LPC mode uses a 5-signal communication interface, a 4-bit address/data bus, LAD[3:0], and a control line, LFRAME#, to control operations of the SST49LF040. Cycle type operations such as Memory Read and Memory Write are defined in Intel Low Pin Count Interface Specification, Revision 1.0. JEDEC Standard SDP (Software Data Protection) Program and Erase commands sequences are incorporated into the standard LPC memory cycles. See Figure 12 through Figure 17 timing diagrams for command sequences.

LPC signals are transmitted via the 4-bit Address/Data bus (LAD[3:0]), and follow a particular sequence, depending on whether they are Read or Write operations. The standard LPC memory cycle is defined in Table 18.

Both LPC Read and Write operations start in a similar way as shown in Figures 10 and 11 timing diagrams. The host (which is the term used here to describe the device driving the memory) asserts LFRAME# for one or more clocks and drives a start value on the LAD[3:0] bus.

At the beginning of an operation, the host may hold the LFRAME# active for several clock cycles, and even change the Start value. The LAD[3:0] bus is latched every rising edge of the clock. On the cycle in which LFRAME# goes inactive, the last latched value is taken as the Start value. CE# must be asserted one cycle before the start cycle to select the SST49LF040 for Read and Write operations.

Once the SST49LF040 identifies the operation as valid (a start value of all zeros), it next expects a nibble that indicates whether this is a memory Read or Write cycle. Once this is received, the device is now ready for the Address and Data cycles. For Write operation the Data cycle will follow the Address cycle, and for Read operation TAR and SYNC cycles occur between the Address and Data cycles. At the end of every operation, the control of the bus must be returned to the host by a 2-clock TAR cycle.

Abort Mechanism

If LFRAME# is driven low for one or more clock cycles during a LPC cycle, the cycle will be terminated and the device will wait for the ABORT command. The host must drive the LAD[3:0] with '1111b' (ABORT command) to return the device to the ready mode. If abort occurs during the internal write cycle, the data may be incorrectly programmed or erased. It is required to wait for the Write operation to complete prior to initiation of the abort command. It is recommended to check the write status with Data# Polling D[7] or Toggle Bit D[6]. One other option is to wait for the fixed write time to expire.

Write Operation Status Detection

The SST49LF040 device provides two software means to detect the completion of a Write (Program or Erase) cycle, in order to optimize the system write cycle time. The software detection includes two status bits: Data# Polling D[7] and Toggle Bit D[6]. The End-of-Write detection mode is incorporated into the LPC Read Cycle. The actual completion of the nonvolatile write is asynchronous with the system; therefore, either a Data# Polling or Toggle Bit read may be simultaneous with the completion of the Write cycle. If this occurs, the system may possibly get an erroneous result, i.e., valid data may appear to conflict with either D[7] or D[6]. In order to prevent spurious rejection, if an erroneous result occurs, the software routine should include a loop to read the accessed location an additional two (2) times. If both Reads are valid, then the device has completed the Write cycle, otherwise the rejection is valid.

Data# Polling

When the SST49LF040 device is in the internal Program operation, any attempt to read D[7] will produce the complement of the true data. Once the Program operation is completed, D[7] will produce true data. Note that even though D[7] may have valid data immediately following the completion of an internal Write operation, the remaining data outputs may still be invalid: valid data on the entire data bus will appear in subsequent successive Read cycles. During internal Erase operation, any attempt to read D[7] will produce a '0'. Once the internal Erase operation is completed, D[7] will produce a '1'. Proper status will not be given using Data# Polling if the address is in the invalid range.

Toggle Bit

During the internal Program or Erase operation, any consecutive attempts to read D[6] will produce alternating 0s and 1s, i.e., toggling between 0 and 1. When the internal Program or Erase operation is completed, the toggling will stop.

System Memory Mapping

The LPC address sequence is 32 bits long. The SST49LF040 will respond to addresses mapped into the top of the 4GB memory space from FFFF FFFFH to FF00 0000H or bottom of the 4GB memory space from 00000 000H to 00FF FFFFFH. Address bits A_{18}-A_0 are decoded as memory addresses for SST49LF040, A_{22}-A_{19} are device ID strapping bits, A_{23} directs Reads and Writes to memory locations (A_{23} = 1) or to register access locations (A_{23} = 0).

Refer to Multiple Device Selection for more detail in device ID strapping decoding. Refer to Figures 4 and 5 for System Memory Boot Configuration.

Multiple Device Selection

Multiple LPC Flash devices may be strapped to increase memory densities in a system. The four ID strapping pins, ID[3:0], allow up to 16 devices to be attached to the same bus by using different ID strapping in a system. Equal density must be used with multiple devices. BIOS support, bus loading or the attaching bridge may limit this number. The maximum "window" of the LPC array visible at one time is 16 MByte.

Applications that boot from the top address of the 4 GByte system memory map; the ID strapping is sequentially incremented downward as shown in Figure 4. For applications that boot from the bottom address of the 4 GByte system memory map, the ID strapping increments upward but non-sequentially as shown in Figure 5.

With hardware strapping, ID bits in the address field is included in every LPC address memory cycle. The address bits [A22: A19] are used to select the device with proper IDs. The ID strapping bits in the address field will be decoded depending on where the device is mapped on the 4 GByte system memory map. See Table 2 for ID address bits decoding. The device will compare these bits with ID[3:0]'s strapping values. If there is a mismatch, the device will ignore the remainder of the cycle.

TABLE 2: ID STRAPPING VALUES FOR SST49LF040

	Hardware Strapping	Address Bits [A_{22}-A_{19}] Decoding[1] 4 GByte System Memory	
Device #	ID[3:0]	Top	Bottom
0 (Boot device)	0000	1111b	0001b
1	0001	1110b	0000b
2	0010	1101b	0011b
3	0011	1100b	0010b
4	0100	1011b	0101b
5	0101	1010b	0100b
6	0110	1001b	0111b
7	0111	1000b	0110b
8	1000	0111b	1001b
9	1001	0110b	1000b
10	1010	0101b	1011b
11	1011	0100b	1010b
12	1100	0011b	1101b
13	1101	0010b	1100b
14	1110	0001b	1111b
15	1111	0000b	1110b

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1. Address bits A_{22}-A_{19} decoding for multiple device selection depends on whether the device is mapped from the top of the 4GB system memory map or from the bottom of the 4GB system memory map.

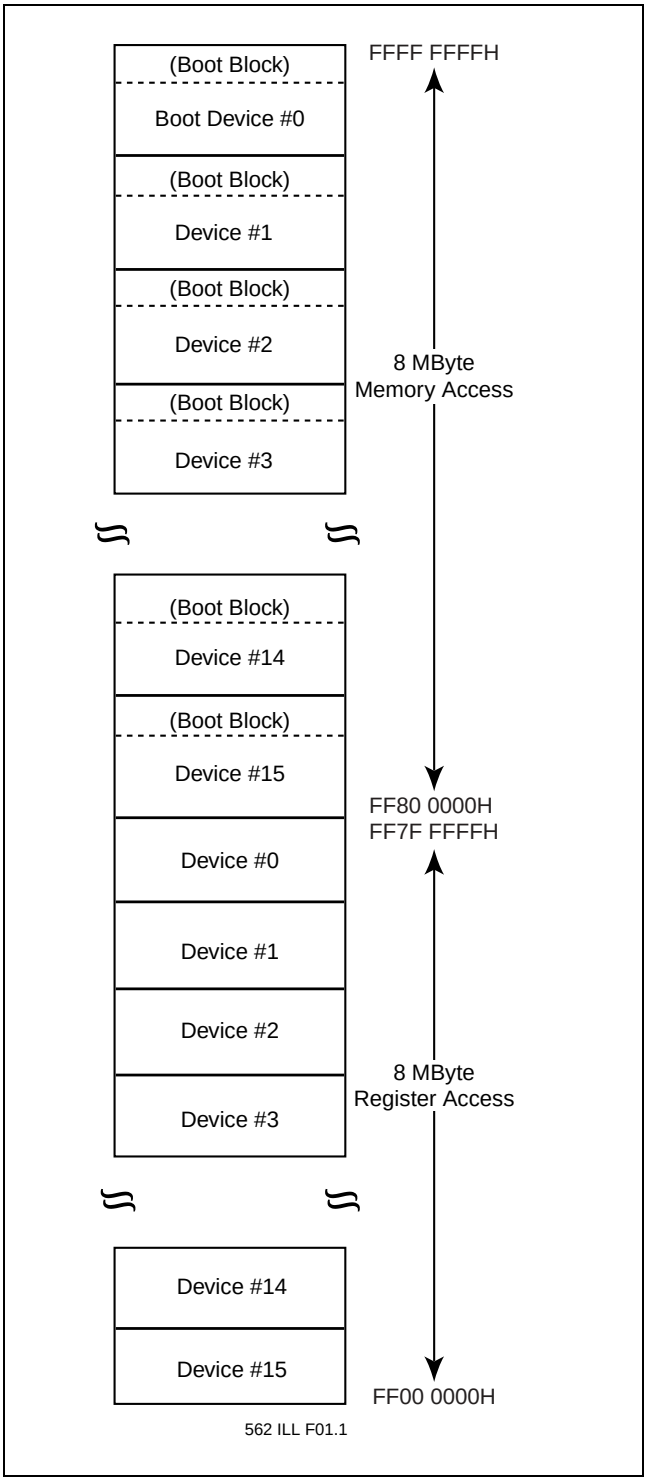

FIGURE 4: BOOT CONFIGURATION FROM THE TOP OF THE 4 GBYTE SYSTEM MEMORY MAP

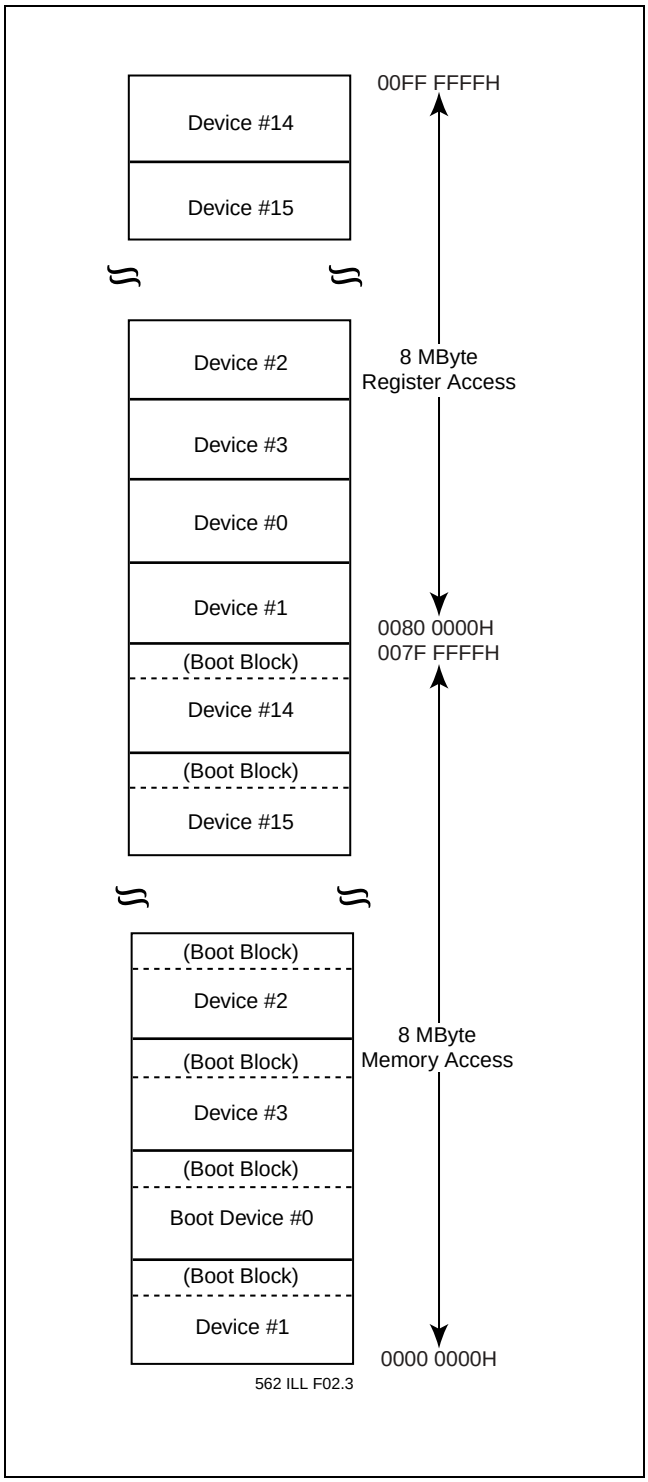

FIGURE 5: BOOT CONFIGURATION FROM THE BOTTOM OF THE 4 GBYTE SYSTEM MEMORY MAP

Registers

There are two registers available on the SST49LF040, the General Purpose Inputs Registers (GPI_REG) and the JEDEC ID Registers. Since multiple LPC memory devices may be used to increase memory densities, these registers appear at its respective address location in the 4 GByte system memory map. Unused register locations will read as 00H. Any attempt to read registers during internal Write operation will respond as "Write Operation Status Detection" (Data# Polling or Toggle Bit). Tables 4 and 5 list GPI_REG and JEDEC ID address locations for SST49LF040 with its respective device strapping.

TABLE 3: GENERAL PURPOSE INPUTS REGISTER

Bit	Function	Pin #	
		32-PLCC	32-TSOP
7:5	Reserved	-	-
4	GPI[4] Reads status of general purpose input pin	30	6
3	GPI[3] Reads status of general purpose input pin	3	11
2	GPI[2] Reads status of general purpose input pin	4	12
1	GPI[1] Reads status of general purpose input pin	5	13
0	GPI[0] Reads status of general purpose input pin	6	14

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General Purpose Inputs Register

The GPI_REG (General Purpose Inputs Register) passes the state of GPI[4:0] pins at power-up on the SST49LF040. It is recommended that the GPI[4:0] pins be in the desired state before LFRAME# is brought low for the beginning of the next bus cycle, and remain in that state until the end of the cycle. There is no default value since this is a pass-through register. See Table 3, General Purpose Inputs Register, for the GPI_REG bits and functions and Tables 4 and 5 for memory address location for its respective device strapping.

JEDEC ID Registers

The JEDEC ID registers identify the device as SST49LF040 and manufacturer as SST in LPC mode. See Tables 4 and 5 for memory address location for its respective JEDEC ID location. Register is not available for Read when the device is in Erase/Program operation. Unused register locations will read as 00H.

TABLE 4: MEMORY MAP REGISTER ADDRESSES (TOP OF THE 4GB SYSTEM MEMORY)

Device #	GPI_REG	JEDEC ID	
		Manufacturer	Device
0	FF7C 0100H	FF7C 0000H	FF7C 0001H
1	FF74 0100H	FF74 0000H	FF74 0001H
2	FF6C 0100H	FF6C 0000H	FF6C 0001H
3	FF64 0100H	FF64 0000H	FF64 0001H
4	FF5C 0100H	FF5C 0000H	FF5C 0001H
5	FF54 0100H	FF54 0000H	FF54 0001H
6	FF4C 0100H	FF4C 0000H	FF4C 0001H
7	FF44 0100H	FF44 0000H	FF44 0001H
8	FF3C 0100H	FF3C 0000H	FF3C 0001H
9	FF34 0100H	FF34 0000H	FF34 0001H
10	FF2C 0100H	FF2C 0000H	FF2C 0001H
11	FF24 0100H	FF24 0000H	FF24 0001H
12	FF1C 0100H	FF1C 0000H	FF1C 0001H
13	FF14 0100H	FF14 0000H	FF14 0001H
14	FF0C 0100H	FF0C 0000H	FF0C 0001H
15	FF04 0100H	FF04 0000H	FF04 0001H

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TABLE 5: MEMORY MAP REGISTER ADDRESSES (BOTTOM OF THE 4GB SYSTEM MEMORY)

Device #	GPI_REG	JEDEC ID	
		Manufacturer	Device
0	008C 0100H	008C 0000H	008C 0001H
1	0084 0100H	0084 0000H	0084 0001H
2	009C 0100H	009C 0000H	009C 0001H
3	0094 0100H	0094 0000H	0094 0001H
4	00AC 0100H	00AC 0000H	00AC 0001H
5	00A4 0100H	00A4 0000H	00A4 0001H
6	00BC 0100H	00BC 0000H	00BC 0001H
7	00B4 0100H	00B4 0000H	00B4 0001H
8	00CC 0100H	00CC 0000H	00CC 0001H
9	00C4 0100H	00C4 0000H	00C4 0001H
10	00DC 0100H	00DC 0000H	00DC 0001H
11	00D4 0100H	00D4 0000H	00D4 0001H
12	00EC 0100H	00EC 0000H	00EC 0001H
13	00E4 0100H	00E4 0000H	00E4 0001H
14	00FC 0100H	00FC 0000H	00FC 0001H
15	00F4 0100H	00F4 0000H	00F4 0001H

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PARALLEL PROGRAMMING MODE

Reset

Driving the RST# low will initiate a hardware reset of the SST49LF040.

Device Operation

Commands are used to initiate the memory operation functions of the device. The data portion of the software command sequence is latched on the rising edge of WE#. During the software command sequence the row address is latched on the falling edge of R/C# and the column address is latched on the rising edge of R/C#.

Read

The Read operation of the SST49LF040 device is controlled by OE#. OE# is the output control and is used to gate data from the output pins. Refer to the Read cycle timing diagram, Figure 19, for further details.

Byte-Program Operation

The SST49LF040 device is programmed on a byte-by-byte basis. Before programming, one must ensure that the sector in which the byte is programmed is fully erased. The Byte-Program operation is initiated by executing a four-byte-command load sequence for Software Data Protection with address (BA) and data in the last byte sequence. During the Byte-Program operation, the row address (A_{10}-A_0) is latched on the falling edge of R/C# and the column address (A_{21}-A_{11}) is latched on the rising edge of R/C#. The data bus is latched on the rising edge of WE#. The Program operation, once initiated, will be completed, within 20 µs. See Figure 23 for Program operation timing diagram and Figure 35 for its flowchart. During the Program operation, the only valid reads are Data# Polling and Toggle Bit. During the internal Program operation, the host is free to perform additional tasks. Any commands written during the internal Program operation will be ignored.

Sector-Erase Operation

The Sector-Erase operation allows the system to erase the device on a sector-by-sector basis. The sector architecture is based on uniform sector size of 4 KByte. The Sector-Erase operation is initiated by executing a six-byte command load sequence for Software Data Protection with Sector-Erase command (30H) and sector address (SA) in the last bus cycle. The internal Erase operation begins after the sixth WE# pulse. The End-of-Erase can be determined using either Data# Polling or Toggle Bit methods. See Figure 24 for Sector-Erase timing waveforms. Any commands written during the Sector-Erase operation will be ignored.

Block-Erase Operation

The Block-Erase Operation allows the system to erase the device in 64 KByte uniform block size. The Block-Erase operation is initiated by executing a six-byte command load sequence for Software Data Protection with Block-Erase command (50H) and block address. The internal Block-Erase operation begins after the sixth WE# pulse. The End-of-Erase can be determined using either Data# Polling or Toggle Bit methods. See Figure 25 for Block-Erase timing waveforms. Any commands written during the Block-Erase operation will be ignored.

Chip-Erase Operation

The SST49LF040 device provides a Chip-Erase operation, which allows the user to erase the entire memory array to the “1s” state. This is useful when the entire device must be quickly erased.

The Chip-Erase operation is initiated by executing a six-byte Software Data Protection command sequence with Chip-Erase command (10H) with address 5555H in the last byte sequence. The internal Erase operation begins with the rising edge of the sixth WE#. During the internal Erase operation, the only valid read is Toggle Bit or Data# Polling. See Table 8 for the command sequence, Figure 26 for Chip-Erase timing diagram, and Figure 38 for the flowchart. Any commands written during the Chip-Erase operation will be ignored.

Write Operation Status Detection

The SST49LF040 device provides two software means to detect the completion of a Write (Program or Erase) cycle, in order to optimize the system write cycle time. The software detection includes two status bits: Data# Polling (DQ_7) and Toggle Bit (DQ_6). The End-of-Write detection mode is enabled after the rising edge of WE# which initiates the internal Program or Erase operation.

The actual completion of the nonvolatile write is asynchronous with the system; therefore, either a Data# Polling or Toggle Bit read may be simultaneous with the completion of the Write cycle. If this occurs, the system may possibly get an erroneous result, i.e., valid data may appear to conflict with either DQ_7 or DQ_6. In order to prevent spurious rejection, if an erroneous result occurs, the software routine should include a loop to read the accessed location an additional two (2) times. If both reads are valid, then the device has completed the Write cycle, otherwise the rejection is valid.

Data# Polling (DQ_7)

When the SST49LF040 device is in the internal Program operation, any attempt to read DQ_7 will produce the complement of the true data. Once the Program operation is completed, DQ_7 will produce true data. Note that even though DQ_7 may have valid data immediately following the completion of an internal Write operation, the remaining data outputs may still be invalid: valid data on the entire data bus will appear in subsequent successive Read cycles after an interval of 1 µs. During internal Erase operation, any attempt to read DQ_7 will produce a '0'. Once the internal Erase operation is completed, DQ_7 will produce a '1'. The Data# Polling is valid after the rising edge of fourth WE# pulse for Program operation. For Sector-, Block-, or Chip-Erase, the Data# Polling is valid after the rising edge of sixth WE# pulse. See Figure 21 for the Data# Polling timing diagram and Figure 36 for a flowchart. Proper status will not be given using Data# Polling if the address is in the invalid range.

Toggle Bit (DQ_6)

During the internal Program or Erase operation, any consecutive attempts to read DQ_6 will produce alternating 0s and 1s, i.e., toggling between 0 and 1. When the internal Program or Erase operation is completed, the toggling will stop. The device is then ready for the next operation. The Toggle Bit is valid after the rising edge of fourth WE# pulse for Program operation. For Sector-, Block-, or Chip-Erase, the Toggle Bit is valid after the rising edge of sixth WE# pulse. See Figure 22 for the Toggle Bit timing diagram and Figure 36 for a flowchart.

Data Protection

The SST49LF040 device provides both hardware and software features to protect nonvolatile data from inadvertent writes.

Hardware Data Protection

Noise/Glitch Protection: A WE# pulse of less than 5 ns will not initiate a Write cycle.

V_{DD} Power Up/Down Detection: The Write operation is inhibited when V_{DD} is less than 1.5V.

Write Inhibit Mode: Forcing OE# low, WE# high will inhibit the Write operation. This prevents inadvertent writes during power-up or power-down.

Software Data Protection (SDP)

The SST49LF040 provides the JEDEC approved Software Data Protection scheme for all data alteration operation, i.e., Program and Erase. Any Program operation requires the inclusion of a series of three-byte sequence. The three-byte load sequence is used to initiate the Program operation, providing optimal protection from inadvertent Write operations, e.g., during the system power-up or power-down. Any Erase operation requires the inclusion of a six-byte load sequence. The SST49LF040 device is shipped with the Software Data Protection permanently enabled. See Table 8 for the specific software command codes. During SDP command sequence, invalid commands will abort the device to Read mode, within T_{RC}.

Electrical Specifications

The AC and DC specifications for the LPC interface signals (LA0[3:0], LFRAME, LCLCK and RST#) as defined in Section 4.2.2.4 of the PCI local Bus specification, Rev. 2.1. Refer to Table 9 for the DC voltage and current specifications. Refer to Tables 13 through 16 and Tables 19 through 21 for the AC timing specifications for Clock, Read, Write, and Reset operations.

Product Identification

The Product Identification mode identifies the device as the SST49LF040 and manufacturer as SST.

TABLE 6: PRODUCT IDENTIFICATION

	Address	Data
Manufacturer's ID	0000H	BFH
Device ID SST49LF040	0001H	51H

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Design Considerations

SST recommends a high frequency 0.1 µF ceramic capacitor to be placed as close as possible between V_{DD} and V_{SS} less than 1 cm away from the V_{DD} pin of the device. Additionally, a low frequency 4.7 µF electrolytic capacitor from V_{DD} to V_{SS} should be placed within 5 cm of the V_{DD} pin. If you use a socket for programming purposes add an additional 1-10 µF next to each socket.

The RST# pin must remain stable at V_{IH} for the entire duration of an Erase operation. WP# must remain stable at V_{IH} for the entire duration of the Erase and Program operations for non-boot block sectors. To write data to the top boot block sectors, the TBL# pin must also remain stable at V_{IH} for the entire duration of the Erase and Program operations.

TABLE 7: OPERATION MODES SELECTION (PP MODE)

Mode	RST#	OE#	WE#	DQ	Address
Read	V_{IH}	V_{IL}	V_{IH}	D_{OUT}	A_{IN}
Program	V_{IH}	V_{IH}	V_{IL}	D_{IN}	A_{IN}
Erase	V_{IH}	V_{IH}	V_{IL}	X[1]	Sector or Block address, XXH for Chip-Erase
Reset	V_{IL}	X	X	High Z	X
Write Inhibit	V_{IH}	V_{IL}	X	High Z/D_{OUT}	X
	X	X	V_{IH}	High Z/D_{OUT}	X
Product Identification	V_{IH}	V_{IL}	V_{IH}	Manufacturer's ID (BFH) Device ID[2]	See Table 8

T7.2 562

1. X can be V_{IL} or V_{IH}, but no other value.
2. Device ID 51H for SST49LF040

TABLE 8: SOFTWARE COMMAND SEQUENCE (ALL INTERFACES)

Command Sequence	1st[1] Cycle		2nd[1] Cycle		3rd[1] Cycle		4th[1] Cycle		5th[1] Cycle		6th[1] Cycle	
	Addr[2]	Data	Addr[2]	Data	Addr[2]	Data	Addr[2]	Data	Addr[2]	Data	Addr[2]	Data
Byte-Program	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	A0H	PA[3]	Data				
Sector-Erase	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	80H	YYYY 5555H	AAH	YYYY 2AAAH	55H	SAx[4]	30H
Block-Erase	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	80H	YYYY 5555H	AAH	YYYY 2AAAH	55H	BAx[5]	50H
Chip-Erase[6]	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	80H	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	10H
Software ID Entry	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	90H	Read ID[7]					
Software ID Exit[8]	XXXX XXXXH	F0H										
Software ID Exit[8]	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	F0H						

T8.3 562

1. LPC mode uses consecutive Write cycles to complete a command sequence; PP mode uses consecutive bus cycles to complete a command sequence.
2. YYYY = A[31:16]
   In LPC mode, during SDP command sequence, YYYY must be within memory address range specified in Figures 4 and 5.
   In PP mode, YYYY can be V_{IL} or V_{IH}.
3. PA = Program Byte address
4. SAx for Sector-Erase Address
5. BAx for Block-Erase Address
6. Chip-Erase is supported in PP mode only
7. SST Manufacturer's ID = BFH, is read with A_0 = 0.
   With A_{18}-A_1 = 0; 49LF040 Device ID = 51H, is read with A_0 = 1.
8. Both Software ID Exit operations are equivalent

Advance Information

Absolute Maximum Stress Ratings (Applied conditions greater than those listed under "Absolute Maximum Stress Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this datasheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Temperature Under Bias . . . . . -55°C to +125°C
Storage Temperature . . . . . -65°C to +150°C
D.C. Voltage on Any Pin to Ground Potential . . . . . -0.5V to V_{DD}+0.5V
Transient Voltage (<20 ns) on Any Pin to Ground Potential . . . . . -2.0V to V_{DD}+2.0V
Package Power Dissipation Capability (Ta=25°C) 1.0W
Surface Mount Lead Soldering Temperature (3 Seconds) . . . . . 240°C
Output Short Circuit Current[1] . . . . . 50 mA

1. Outputs shorted for no more than one second. No more than one output shorted at a time.

OPERATING RANGE

Range	Ambient Temp	V_{DD}
Commercial	0°C to +85°C	3.0-3.6V

AC CONDITIONS OF TEST

Input Rise/Fall Time	3 ns
Output Load	C_L = 30 pF
See Figures 29 and 30	

TABLE 9: DC OPERATING CHARACTERISTICS (ALL INTERFACE)

Symbol	Parameter	Limits			Test Conditions[1]
		Min	Max	Units	
I_{DD}	Active V_{DD} Current				Address input=V_{IL}/V_{IH}, at f=1/T_{RC} Min, V_{DD}=V_{DD} Max
	Read		12	mA	OE#=V_{IL}, WE#=V_{IH}, All I/Os open
	Write[2]		24	mA	OE#=V_{IH}, V_{DD}=V_{DD} Max
I_{SB}	Standby V_{DD} Current (LPC Interface)		100	µA	LFRAME#=0.9 V_{DD}, f=33 MHz, CE#=0.9 V_{DD} V_{DD}=V_{DD} Max, All other inputs ≥ 0.9 V_{DD} or ≤ 0.1 V_{DD}
I_{RY}[3]	Ready Mode V_{DD} Current (LPC Interface)		10	mA	LFRAME#=V_{IL}, f=33 MHz, V_{DD}=V_{DD} Max All other inputs ≥ 0.9 V_{DD} or ≤ 0.1 V_{DD}
I_I	Input Current for IC: ID[3:0] pins for SST49LF040 ID[3:1] pins for SST49LF080A		200	µA	V_{IN}=GND to V_{DD}, V_{DD}=V_{DD} Max
I_{LI}	Input Leakage Current		1	µA	V_{IN}=GND to V_{DD}, V_{DD}=V_{DD} Max
I_{LO}	Output Leakage Current		1	µA	V_{OUT}=GND to V_{DD}, V_{DD}=V_{DD} Max
V_{IHI}	INIT# Input High Voltage	1.1	V_{DD}+0.5	V	V_{DD}=V_{DD} Max
V_{ILI}	INIT# Input Low Voltage	-0.5	0.4	V	V_{DD}=V_{DD} Min
V_{IL}	Input Low Voltage	-0.5	0.3 V_{DD}	V	V_{DD}=V_{DD} Min
V_{IH}	Input High Voltage	0.5 V_{DD}	V_{DD}+0.5	V	V_{DD}=V_{DD} Max
V_{OL}	Output Low Voltage		0.1 V_{DD}	V	I_{OL}=1500µA, V_{DD}=V_{DD} Min
V_{OH}	Output High Voltage	0.9 V_{DD}		V	I_{OH}=-500 µA, V_{DD}=V_{DD} Min

T9.2 562

1. Test conditions apply to PP mode.
2. I_{DD} active while Erase or Program is in progress.
3. The device is in Ready Mode when no activity is on the LPC bus.

TABLE 10: RECOMMENDED SYSTEM POWER-UP TIMINGS

Symbol	Parameter	Minimum	Units
$T_{PU-READ}$[1]	Power-up to Read Operation	100	µs
$T_{PU-WRITE}$[1]	Power-up to Write Operation	100	µs

T10.0 562

1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter

TABLE 11: PIN CAPACITANCE (V_{DD}=3.3V, Ta=25 °C, f=1 Mhz, other pins open)

Parameter	Description	Test Condition	Maximum
$C_{I/O}$[1]	I/O Pin Capacitance	$V_{I/O}$=0V	12 pF
C_{IN}[1]	Input Capacitance	V_{IN}=0V	6 pF

T11.0 562

1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 12: RELIABILITY CHARACTERISTICS

Symbol	Parameter	Minimum Specification	Units	Test Method
N_{END}[1]	Endurance	10,000	Cycles	JEDEC Standard A117
T_{DR}[1]	Data Retention	100	Years	JEDEC Standard A103
I_{LTH}[1]	Latch Up	100 + I_{DD}	mA	JEDEC Standard 78

T12.0 562

1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 13: CLOCK TIMING PARAMETERS (LPC MODE)

Symbol	Parameter	Min	Max	Units
T_{CYC}	LCLK Cycle Time	30		ns
T_{HIGH}	LCLK High Time	11		ns
T_{LOW}	LCLK Low Time	11		ns
-	LCLK Slew Rate (peak-to-peak)	1	4	V/ns
-	RST# or INIT# Slew Rate	50		mV/ns

T13.0 562

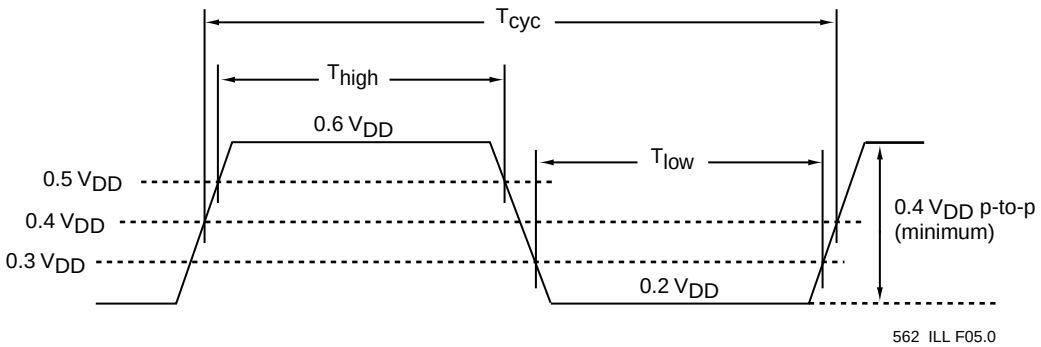

FIGURE 6: LCLK WAVEFORM

TABLE 14: RESET TIMING PARAMETERS (LPC MODE), V_{DD}=3.0-3.6V

Symbol	Parameter	Min	Max	Units
T_{PRST}	V_{DD} stable to Reset Low	1		ms
T_{KRST}	Clock Stable to Reset Low	100		µs
T_{RSTP}	RST# Pulse Width	100		ns
T_{RSTF}	RST# Low to Output Float		48	ns
T_{RST}[1]	RST# High to LFRAME# Low	1		µs
T_{RSTE}	RST# Low to reset during Sector-/Block-Erase or Program		10	µs

T14.0 562

1. There will be a latency of T_{RSTE} if a reset procedure is performed during a programming or erase operation,

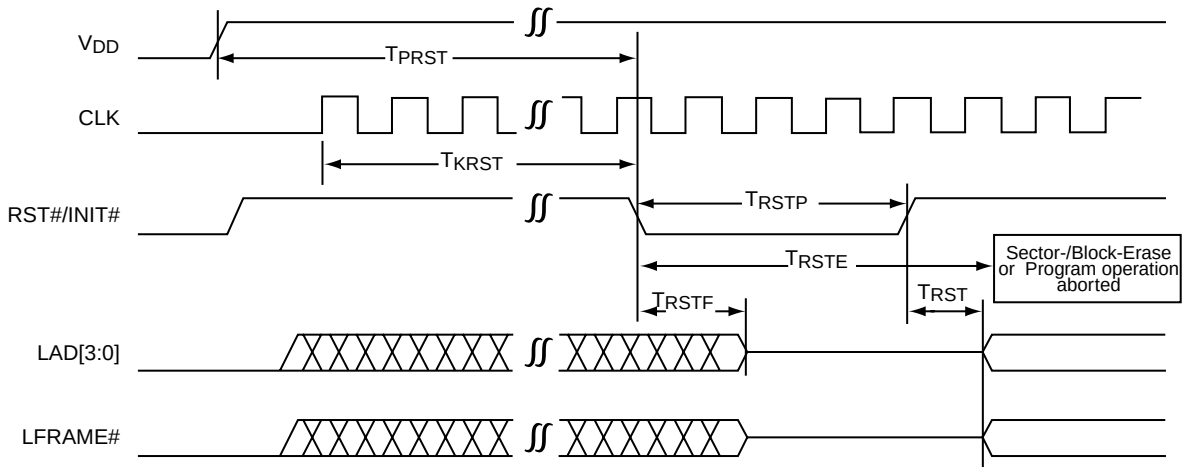

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FIGURE 7: RESET TIMING DIAGRAM

AC CHARACTERISTICS (LPC MODE)

TABLE 15: READ/WRITE CYCLE TIMING PARAMETERS (LPC MODE), V_{DD}=3.0-3.6V

Symbol	Parameter	Min	Max	Units
T_{CYC}	Clock Cycle Time	30		ns
T_{SU}	Data Set Up Time to Clock Rising	7		ns
T_{DH}	Clock Rising to Data Hold Time	0		ns
T_{VAL}[1]	Clock Rising to Data Valid	2	11	ns
T_{BP}	Byte Programming Time		20	µs
T_{SE}	Sector-Erase Time		25	ms
T_{BE}	Block-Erase Time		25	ms
T_{ON}	Clock Rising to Active (Float to Active Delay)	2		ns
T_{OFF}	Clock Rising to Inactive (Active to Float Delay)		28	ns

T15.0 562

1. Minimum and maximum times have different loads. See PCI spec

TABLE 16: AC INPUT/OUTPUT SPECIFICATIONS (LPC MODE)

Symbol	Parameter	Min	Max	Units	Conditions
I_{OH}(AC)	Switching Current High	-12 V_{DD}		mA	$0 < V_{OUT} \leq 0.3V_{DD}$
		-17.1(V_{DD}-V_{OUT})		mA	$0.3V_{DD} < V_{OUT} < 0.9V_{DD}$
			Equation C[1]		$0.7V_{DD} < V_{OUT} < V_{DD}$
	(Test Point)		-32 V_{DD}	mA	$V_{OUT} = 0.7V_{DD}$
I_{OL}(AC)	Switching Current Low	16 V_{DD}	Equation D[1]	mA	$V_{DD} > V_{OUT} \geq 0.6V_{DD}$
		26.7 V_{OUT}		mA	$0.6V_{DD} > V_{OUT} > 0.1V_{DD}$
					$0.18V_{DD} > V_{OUT} > 0$
	(Test Point)		38 V_{DD}	mA	$V_{OUT} = 0.18V_{DD}$
I_{CL}	Low Clamp Current	-25+(V_{IN}+1)/0.015		mA	$-3 < V_{IN} \leq -1$
I_{CH}	High Clamp Current	25+(V_{IN}-V_{DD}-1)/0.015		mA	$V_{DD}+4 > V_{IN} \geq V_{DD}+1$
slewr[2]	Output Rise Slew Rate	1	4	V/ns	$0.2V_{DD}$-$0.6V_{DD}$ load
slewf[2]	Output Fall Slew Rate	1	4	V/ns	$0.6V_{DD}$-$0.2V_{DD}$ load

T16.0 562

1. See PCI spec.
2. PCI specification output load is used.

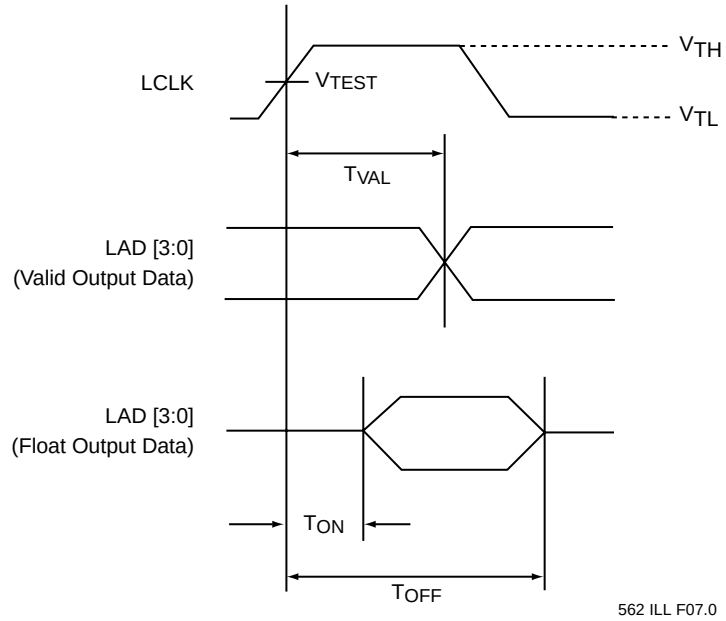

FIGURE 8: OUTPUT TIMING PARAMETERS

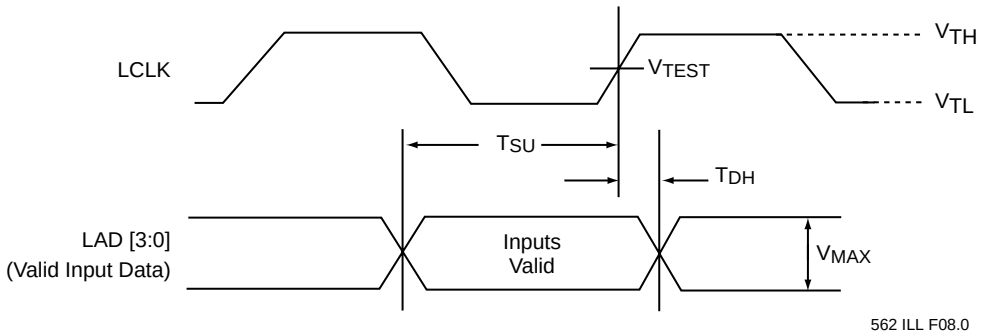

FIGURE 9: INPUT TIMING PARAMETERS

TABLE 17: INTERFACE MEASUREMENT CONDITION PARAMETERS

Symbol	Value	Units
V_{TH}[1]	0.6 V_{DD}	V
V_{TL}[1]	0.2 V_{DD}	V
V_{TEST}	0.4 V_{DD}	V
V_{MAX}[1]	0.4 V_{DD}	V
Input Signal Edge Rate	1 V/ns	

T17.0 562

1. The input test environment is done with 0.1 V_{DD} of overdrive over V_{IH} and V_{IL}. Timing parameters must be met with no more overdrive than this. V_{MAX} specified the maximum peak-to-peak waveform allowed for measuring input timing. Production testing may use different voltage values, but must correlate results back to these parameters

TABLE 18: STANDARD LPC MEMORY CYCLE DEFINITION (LPC MODE)

Field	No. of Clocks	Description
START	1	"0000b" appears on LPC bus to indicate the start of cycle
CYCTYPE + DIR	1	Cycle Type: Indicates the type of cycle. Bits 3:2 must be "01b" for memory cycle. Bit 1 indicates the type of transfer "0" for Read, "1" for write. DIR: Indicates the direction of the transfer. "0b" for Read, "1b" for Write. Bit 0 is reserved. "010Xb" indicates memory Read cycle; while "011xb" indicates memory Write cycle.
TAR	2	The last component driving LAD[3:0] will drive it to "1111b" during the first clock, and tri-state it during the second clock.
ADDR	8	Address Phase for Memory Cycle. LPC supports the 32-bit address protocol. The addresses transfer most significant nibble first and least significant nibble last. (i.e., Address[31:28] on LAD[3:0] first, and Address[3:0] on LAD[3:0] last.)
Sync	N	Synchronize to host or peripheral by adding wait states. "0000b" means Ready, "0101b" means Short Wait, "0110b" means Long Wait, "1001b" for DMA only, "1010b" means error, other values are reserved. The SST49LF040 only supports "Ready" sync.
Data	2	Data Phase for Memory Cycle. **The data transfer least significant nibble first and most significant nibble last.** (i.e., DQ[3:0] on LAD[3:0] first, then DQ[7:4] on LAD[3:0] last.)

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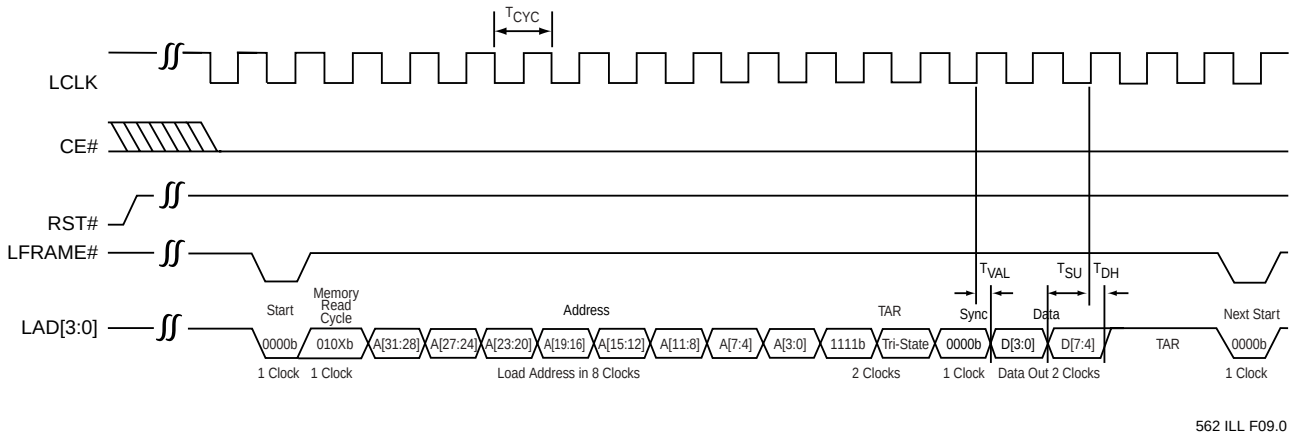


FIGURE 10: READ CYCLE TIMING DIAGRAM (LPC MODE)

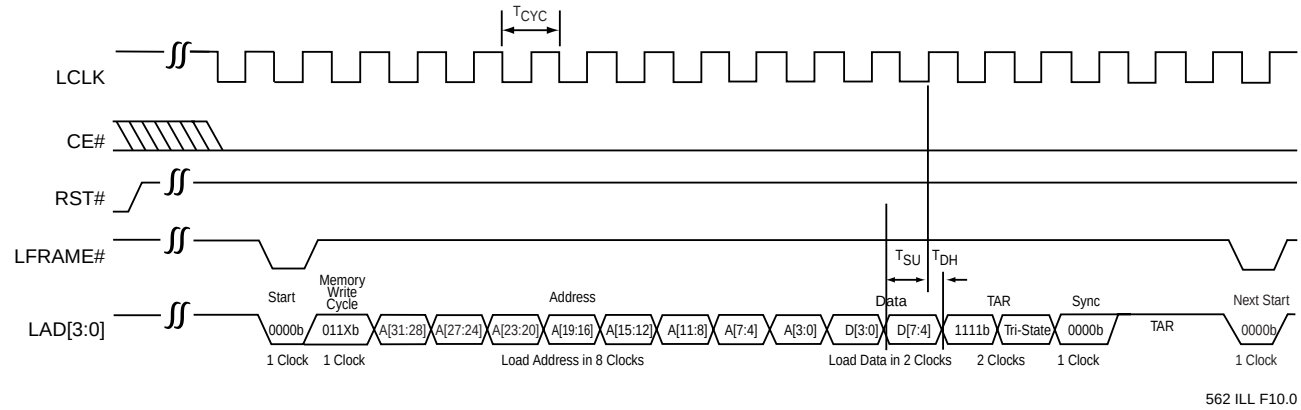
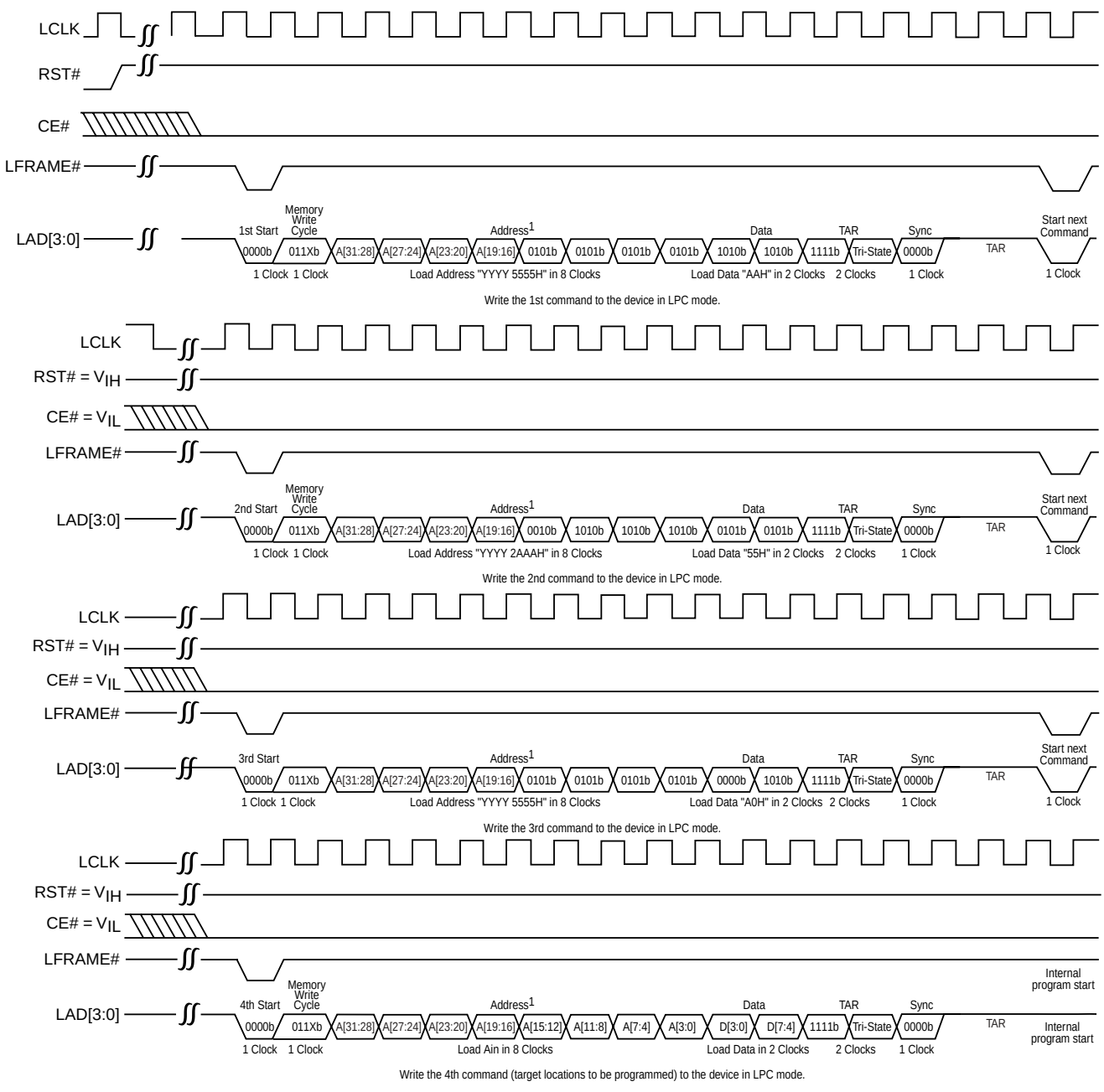
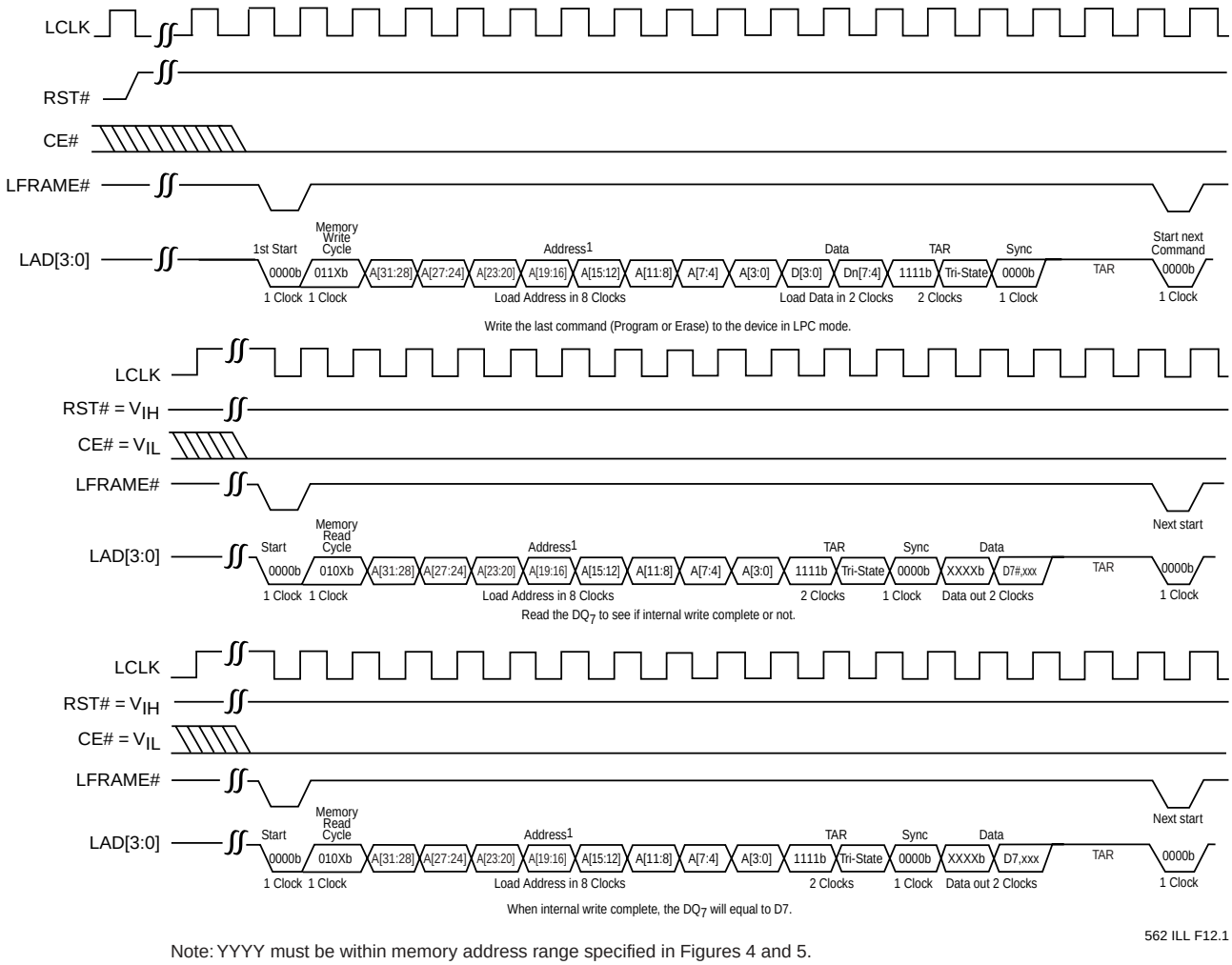


FIGURE 11: WRITE CYCLE TIMING DIAGRAM (LPC MODE)



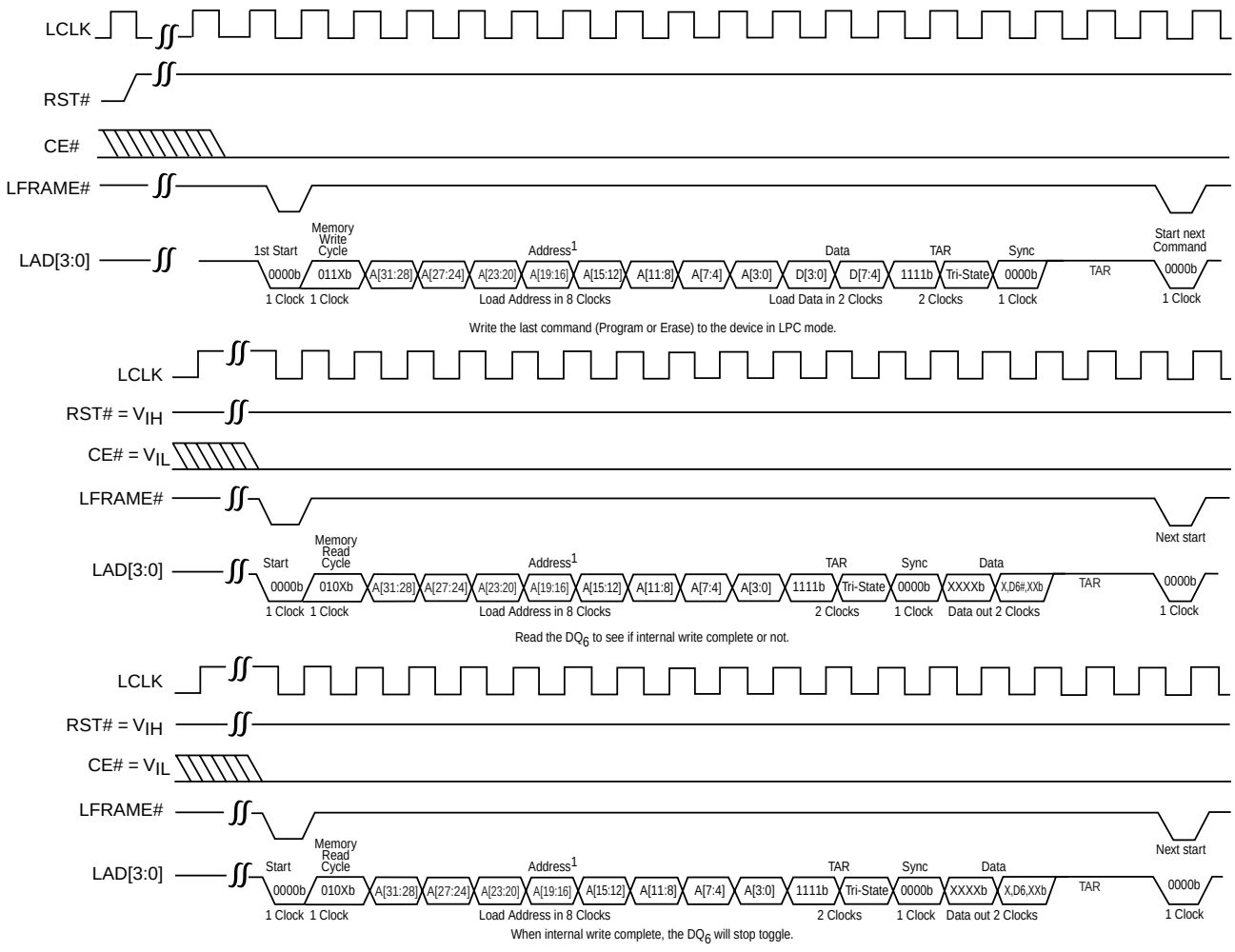
Note 1: YYYYH must be within memory address range specified in Figures 4 and 5.

FIGURE 12: PROGRAM CYCLE TIMING DIAGRAM (LPC MODE)



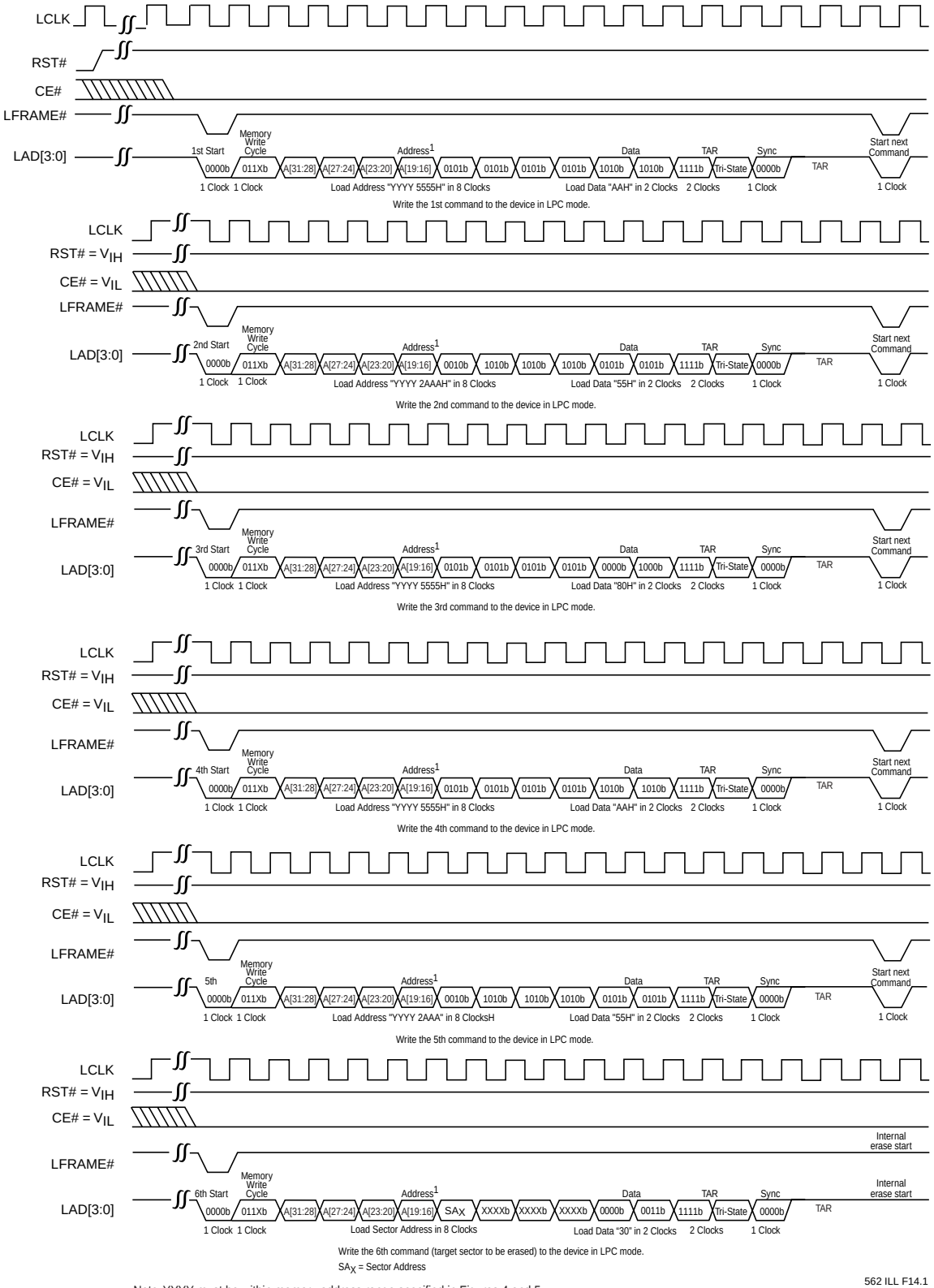
Note: YYYY must be within memory address range specified in Figures 4 and 5.

FIGURE 13: DATA# POLLING TIMING DIAGRAM (LPC MODE)



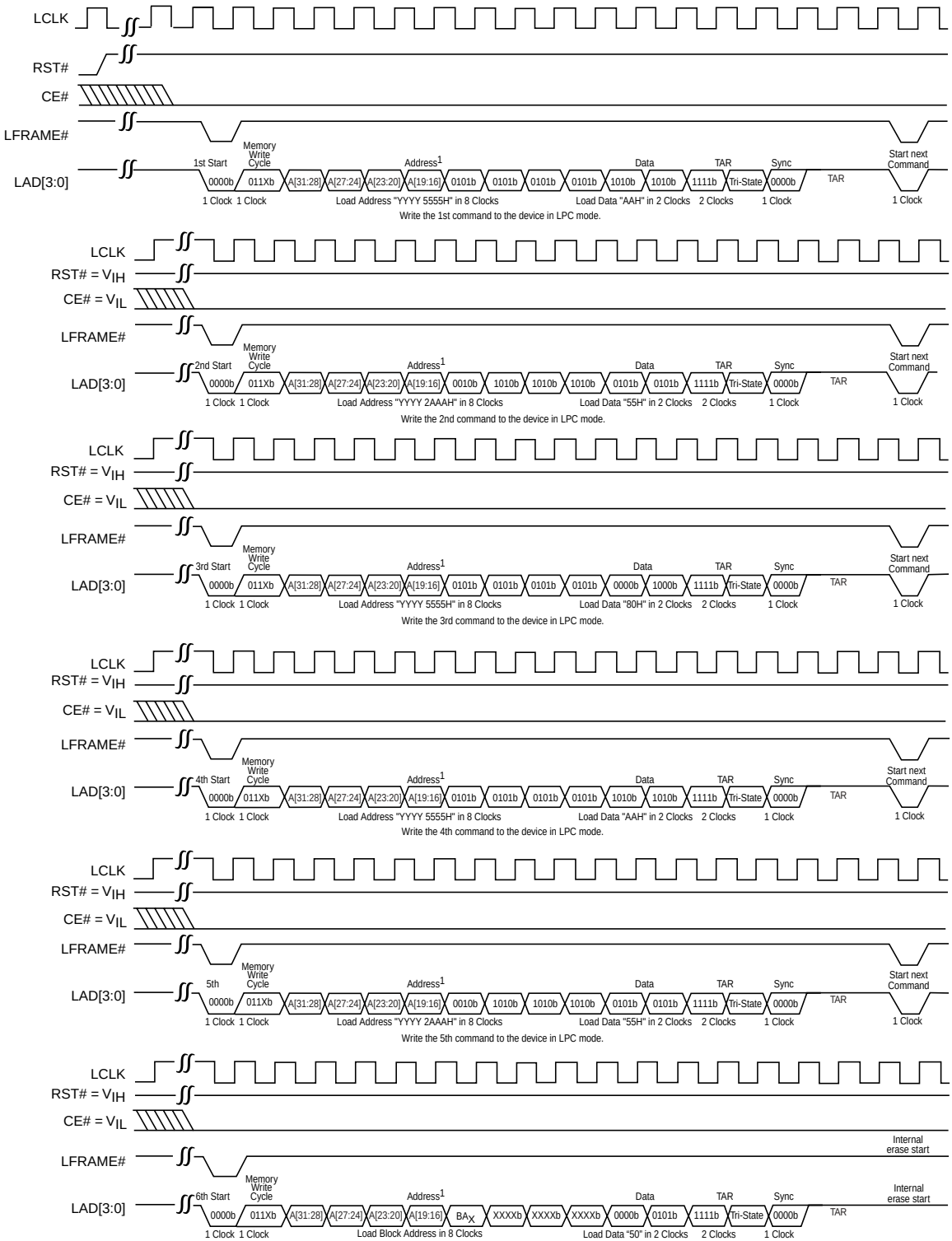
Note: YYYY must be within memory address range specified in Figures 4 and 5.

FIGURE 14: TOGGLE BIT TIMING DIAGRAM (LPC MODE)



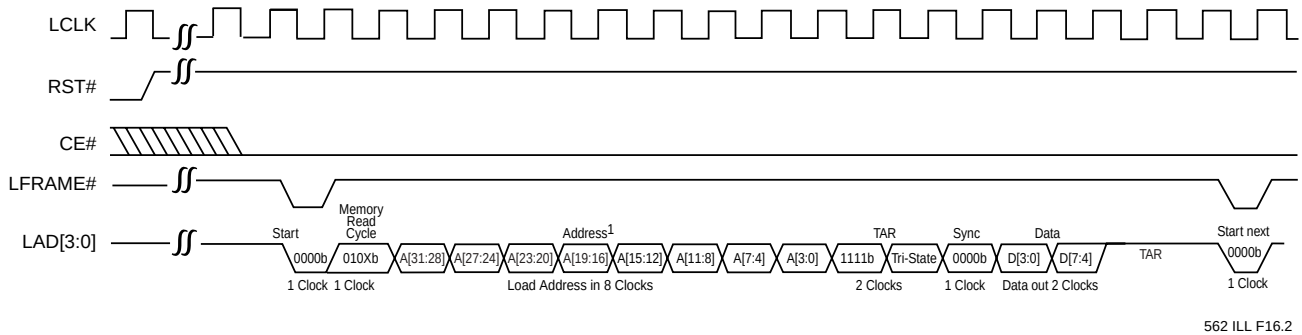
Note: YYYY must be within memory address range specified in Figures 4 and 5.

FIGURE 15: SECTOR-ERASE TIMING DIAGRAM (LPC MODE)



Note: YYYY must be within memory address range specified in Figures 4 and 5.

FIGURE 16: BLOCK-ERASE TIMING DIAGRAM (LPC MODE)



Note: See Tables 4 and 5 Register Addresses

FIGURE 17: GPI REGISTER READOUT TIMING DIAGRAM (LPC MODE)

AC CHARACTERISTICS (PP MODE)

TABLE 19: READ CYCLE TIMING PARAMETERS (PP MODE), V_{DD}=3.0-3.6V

Symbol	Parameter	Min	Max	Units
T_{RC}	Read Cycle Time	270		ns
T_{RST}	RST# High to Row Address Setup	1		µs
T_{AS}	R/C# Address Set-up Time	45		ns
T_{AH}	R/C# Address Hold Time	45		ns
T_{AA}	Address Access Time		120	ns
T_{OE}	Output Enable Access Time		60	ns
T_{OLZ}	OE# Low to Active Output	0		ns
T_{OHZ}	OE# High to High-Z Output		35	ns
T_{OH}	Output Hold from Address Change	0		ns

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TABLE 20: PROGRAM/ERASE CYCLE TIMING PARAMETERS (PP MODE), V_{DD}=3.0-3.6V

Symbol	Parameter	Min	Max	Units
T_{RST}	RST# High to Row Address Setup	1		µs
T_{AS}	R/C# Address Setup Time	50		ns
T_{AH}	R/C# Address Hold Time	50		ns
T_{CWH}	R/C# to Write Enable High Time	50		ns
T_{OES}	OE# High Setup Time	20		ns
T_{OEH}	OE# High Hold Time	20		ns
T_{OEP}	OE# to Data# Polling Delay		40	ns
T_{OET}	OE# to Toggle Bit Delay		40	ns
T_{WP}	WE# Pulse Width	100		ns
T_{WPH}	WE# Pulse Width High	100		ns
T_{DS}	Data Setup Time	50		ns
T_{DH}	Data Hold Time	5		ns
T_{IDA}	Software ID Access and Exit Time		150	ns
T_{BP}	Byte Programming Time		20	µs
T_{SE}	Sector-Erase Time		25	ms
T_{BE}	Block-Erase Time		25	ms
T_{SCE}	Chip-Erase Time		100	ms

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TABLE 21: RESET TIMING PARAMETERS (PP MODE), V_{DD}=3.0-3.6V

Symbol	Parameter	Min	Max	Units
T_{PRST}	V_{DD} stable to Reset Low	1		ms
T_{RSTP}	RST# Pulse Width	100		ns
T_{RSTF}	RST# Low to Output Float		48	ns
T_{RST}[1]	RST# High to Row Address Setup	1		µs
T_{RSTE}	RST# Low to reset during Sector-/Block-Erase or Program		10	µs
T_{RSTC}	RST# Low to reset during Chip-Erase		50	µs

T21.0 562

1. There will be a reset latency of T_{RSTE} or T_{RSTC} if a reset procedure is performed during a programming or erase operational.

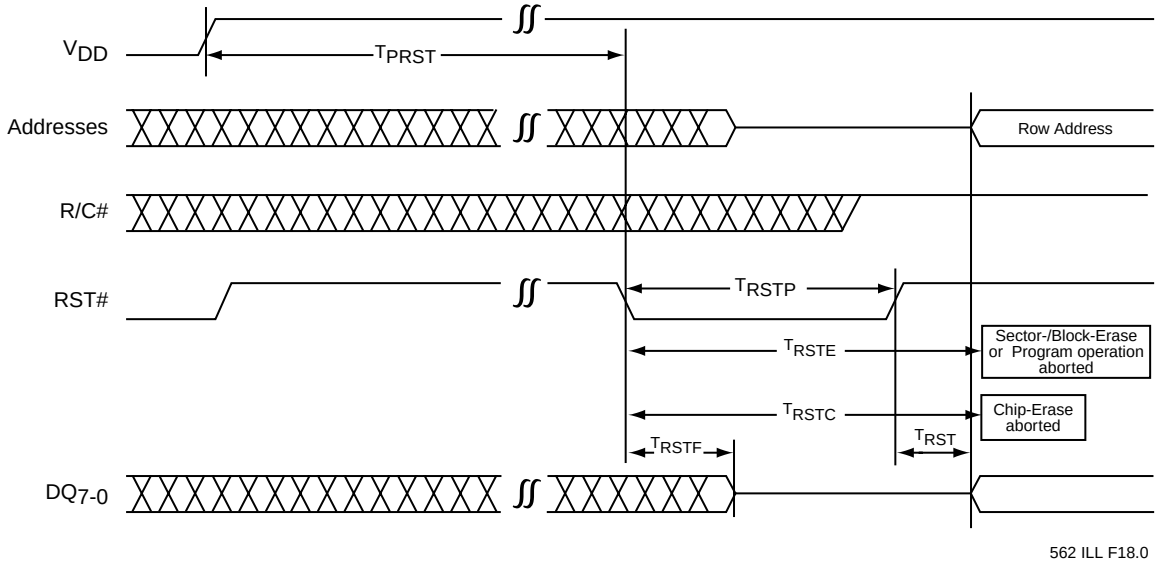


FIGURE 18: RESET TIMING DIAGRAM

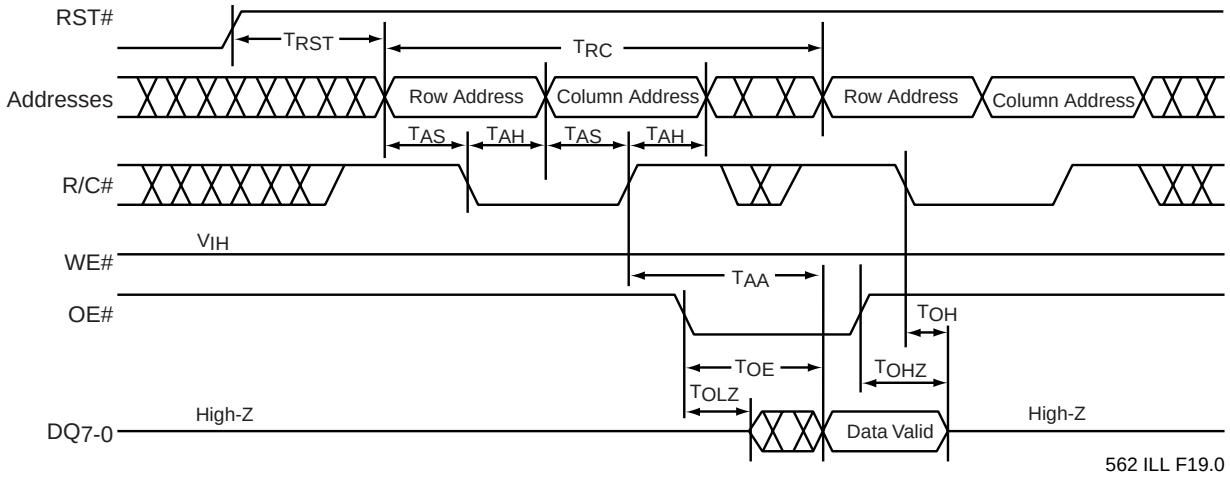


FIGURE 19: READ CYCLE TIMING DIAGRAM (PP MODE)

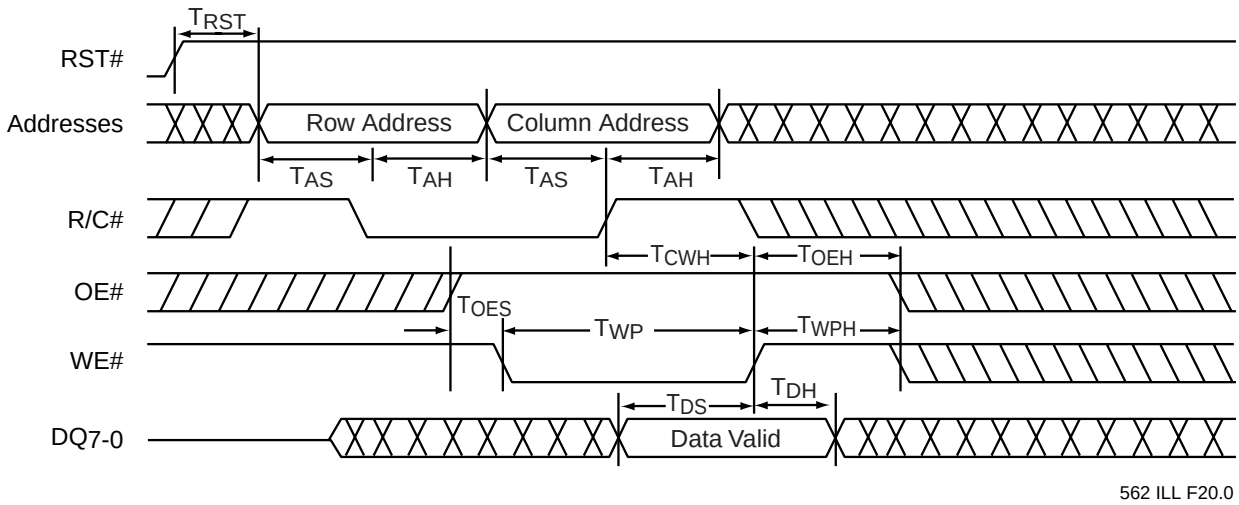


FIGURE 20: WRITE CYCLE TIMING DIAGRAM (PP MODE)

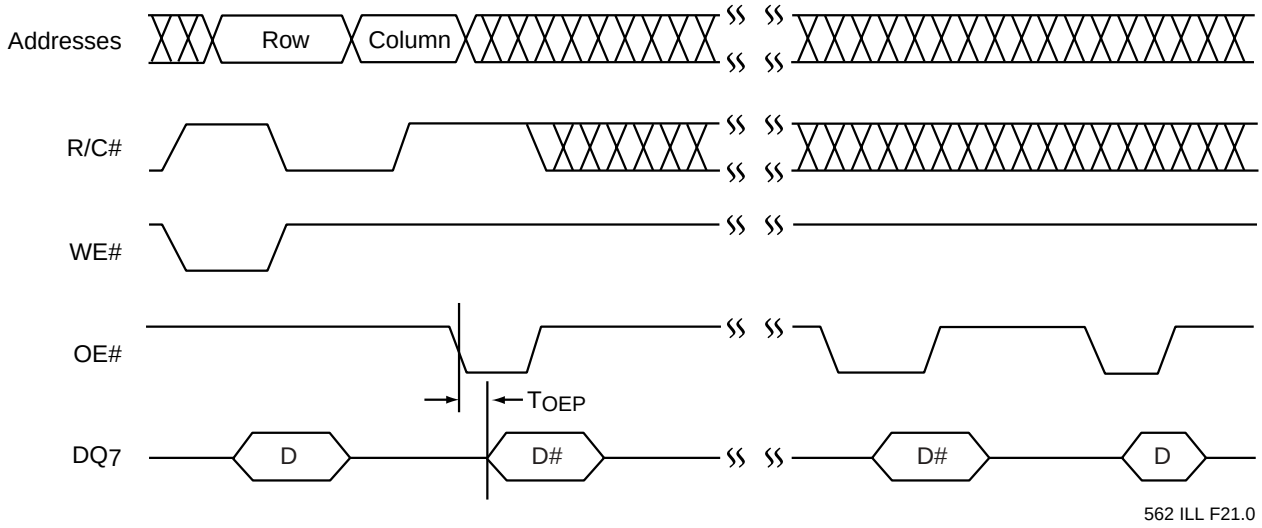


FIGURE 21: DATA# POLLING TIMING DIAGRAM (PP MODE)

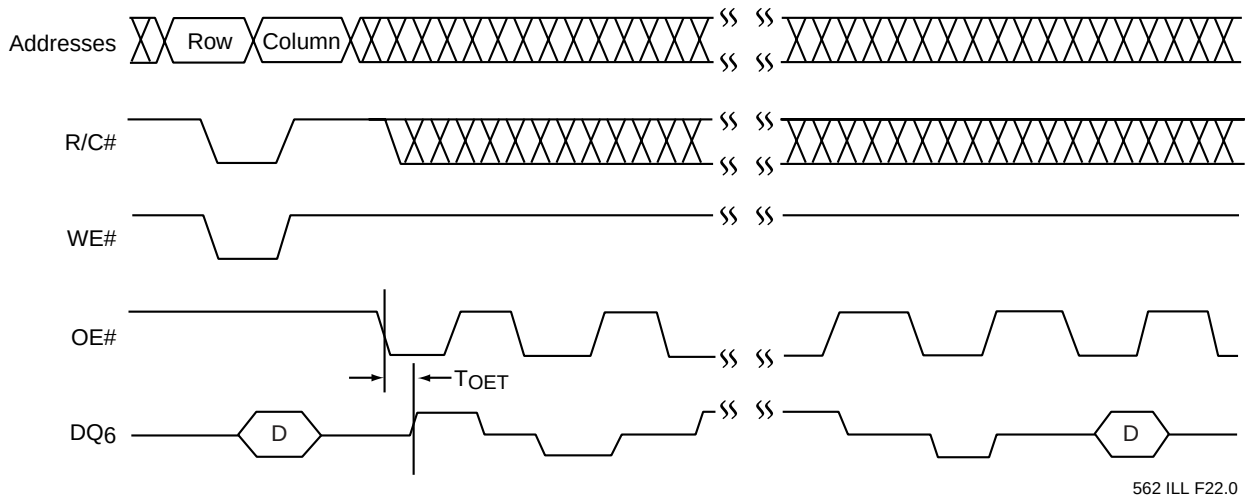


FIGURE 22: TOGGLE BIT TIMING DIAGRAM (PP MODE)

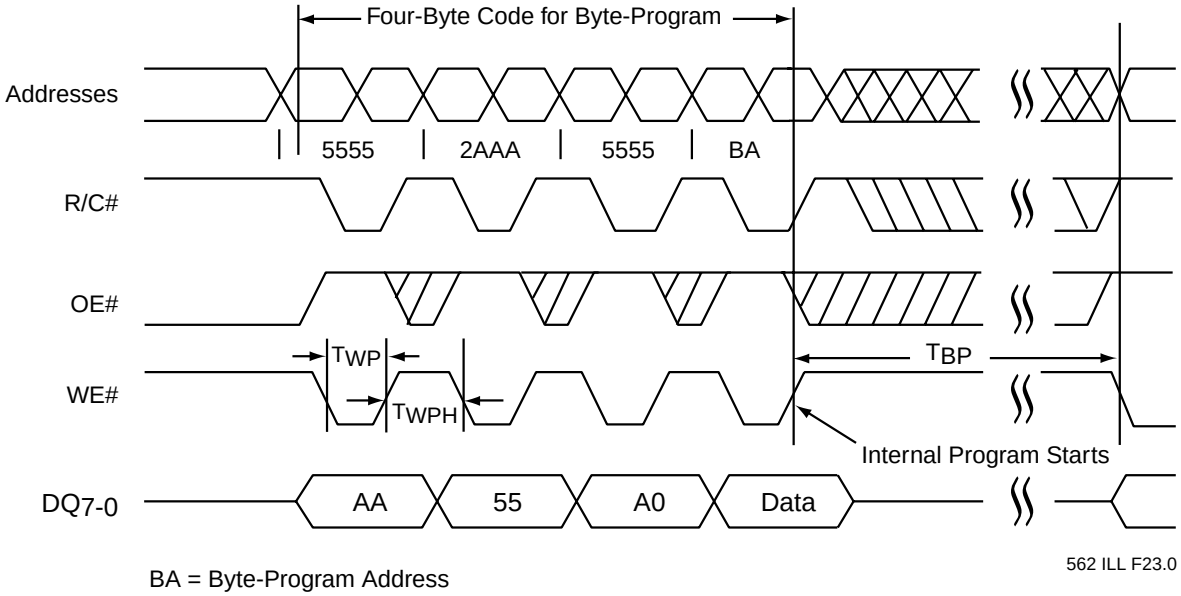


FIGURE 23: BYTE-PROGRAM TIMING DIAGRAM (PP MODE)

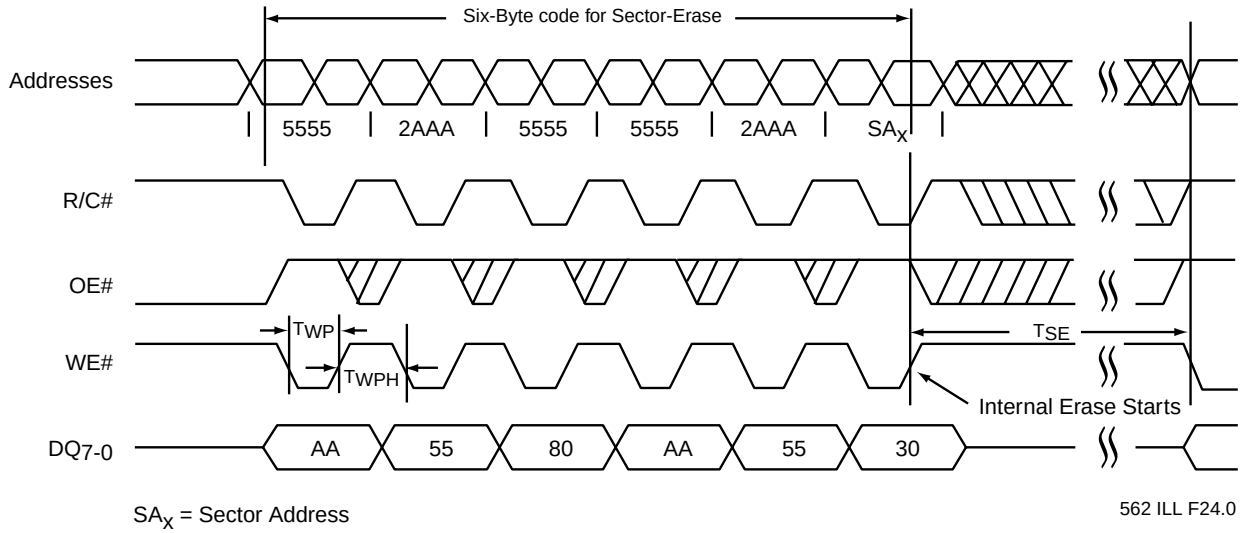


FIGURE 24: SECTOR-ERASE TIMING DIAGRAM (PP MODE)

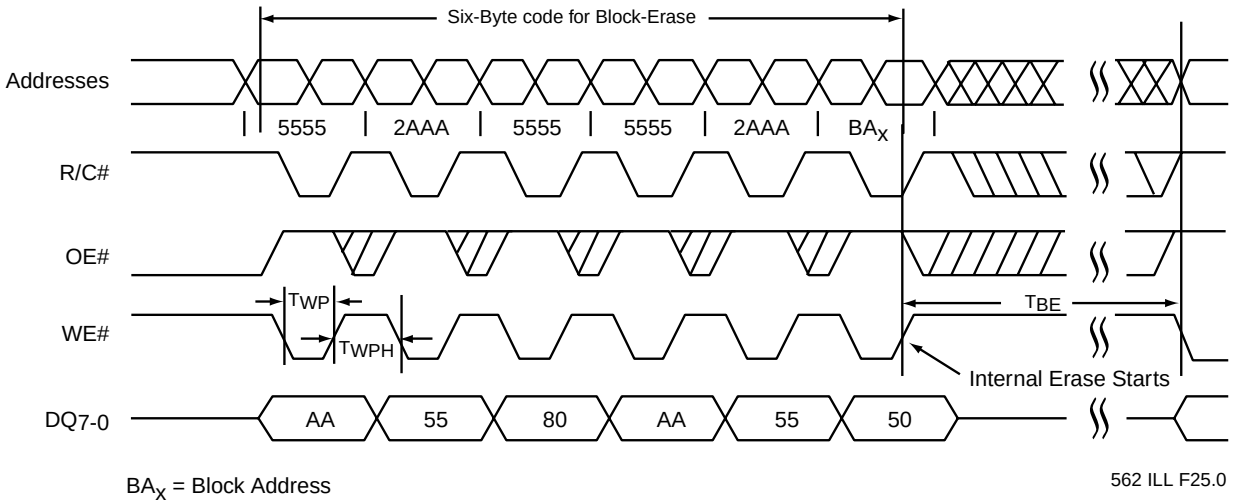


FIGURE 25: BLOCK-ERASE TIMING DIAGRAM (PP MODE)

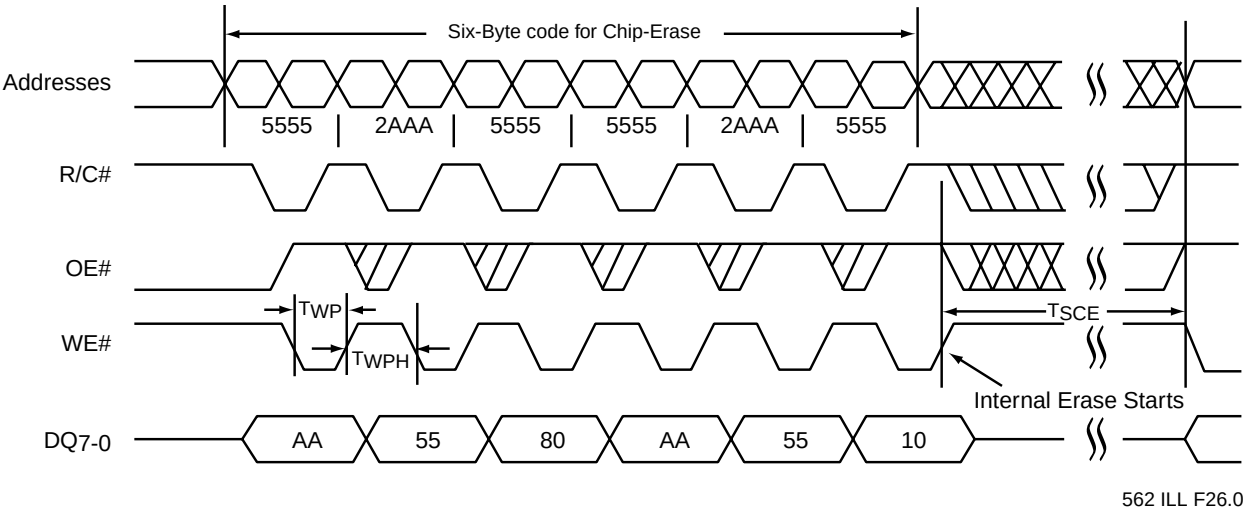
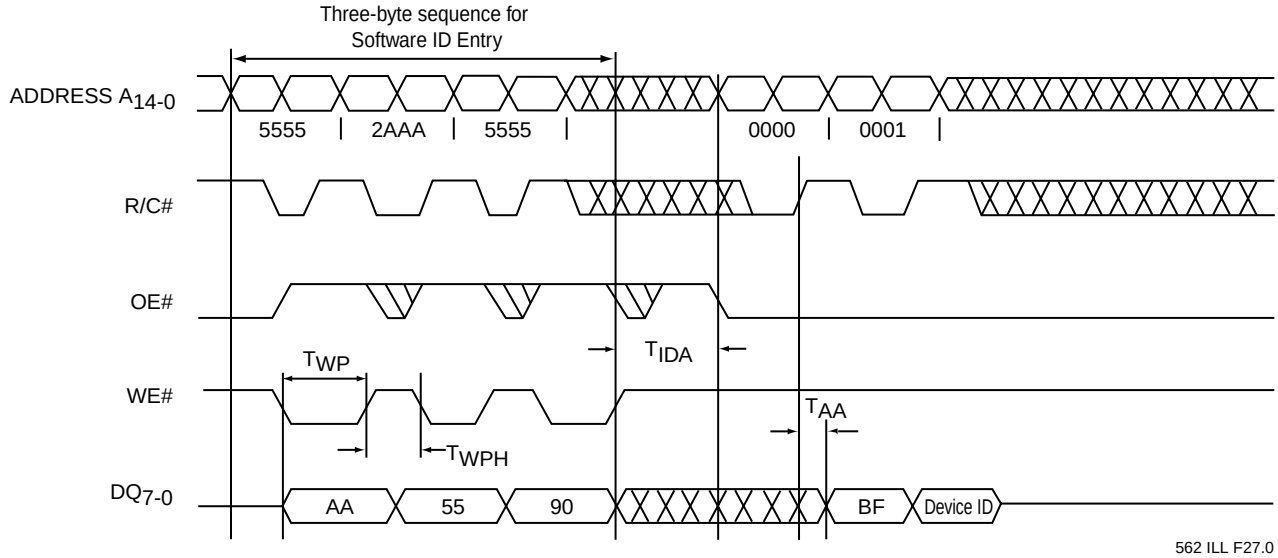


FIGURE 26: CHIP-ERASE TIMING DIAGRAM (PP MODE)



Device ID = 51H for SST49LF040A and 5BH for SST49LF080A

FIGURE 27: SOFTWARE ID ENTRY AND READ (PP MODE)

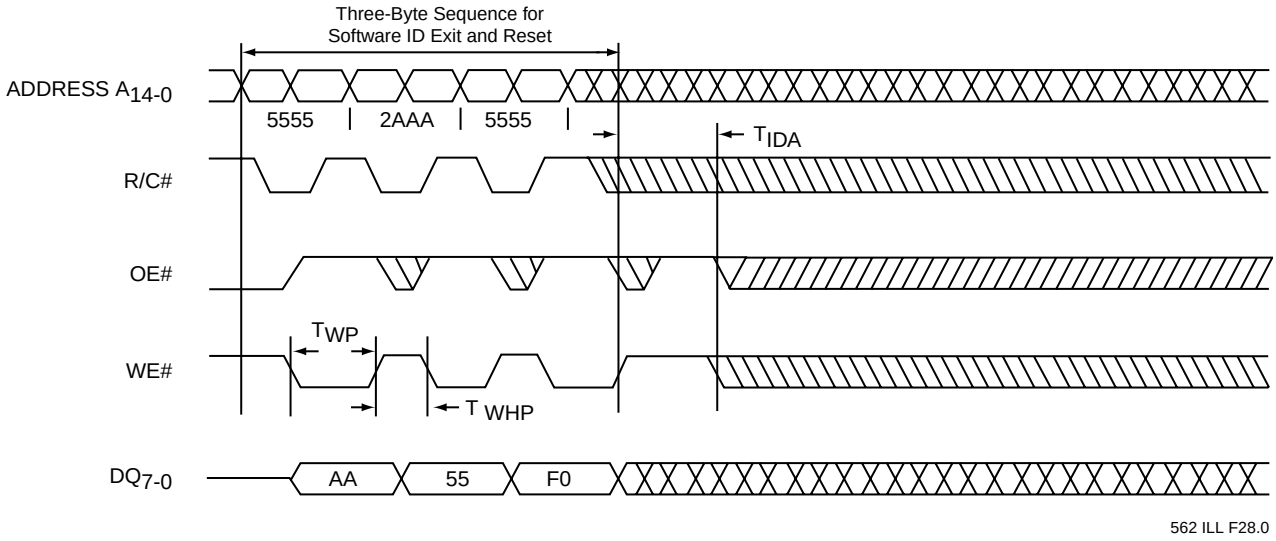
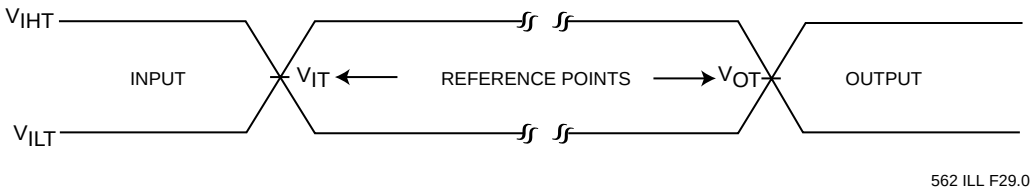


FIGURE 28: SOFTWARE ID EXIT AND RESET (PP MODE)



AC test inputs are driven at V_{IHT} (0.9 V_{DD}) for a logic "1" and V_{ILT} (0.1 V_{DD}) for a logic "0". Measurement reference points for inputs and outputs are V_{IT} (0.5 V_{DD}) and V_{OT} (0.5 V_{DD}). Input rise and fall times (10% ↔ 90%) are <5 ns.

Note: V_{IT} - V_{INPUT} Test
V_{OT} - V_{OUTPUT} Test
V_{IHT} - V_{INPUT} HIGH Test
V_{ILT} - V_{INPUT} LOW Test

FIGURE 29: AC INPUT/OUTPUT REFERENCE WAVEFORMS

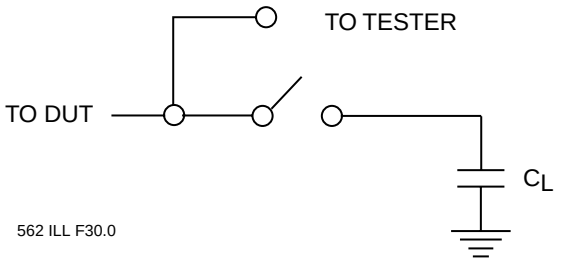


FIGURE 30: A TEST LOAD EXAMPLE

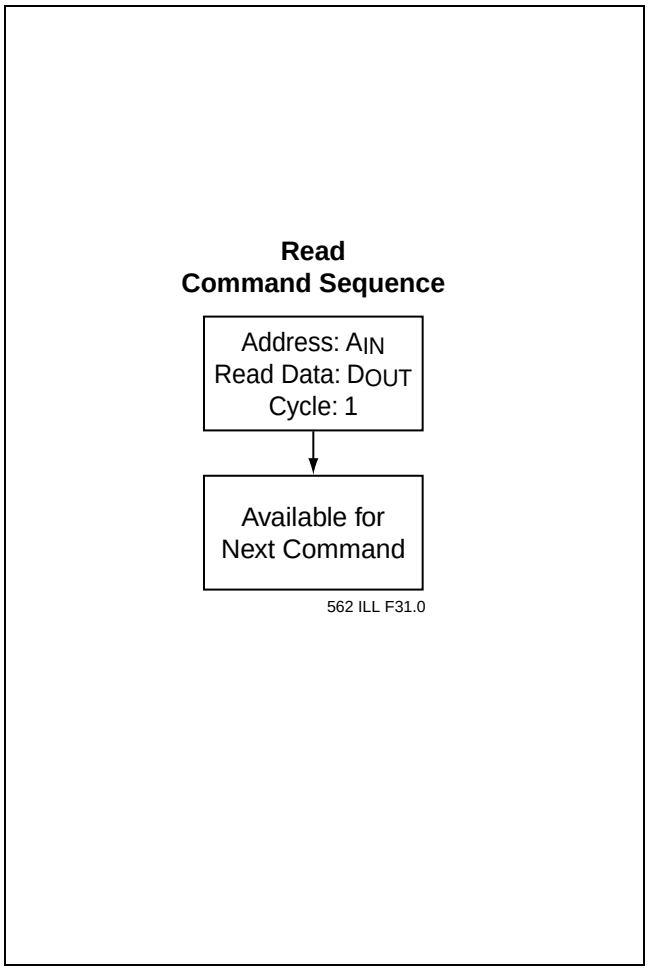


FIGURE 31: READ COMMAND SEQUENCE (LPC MODE)

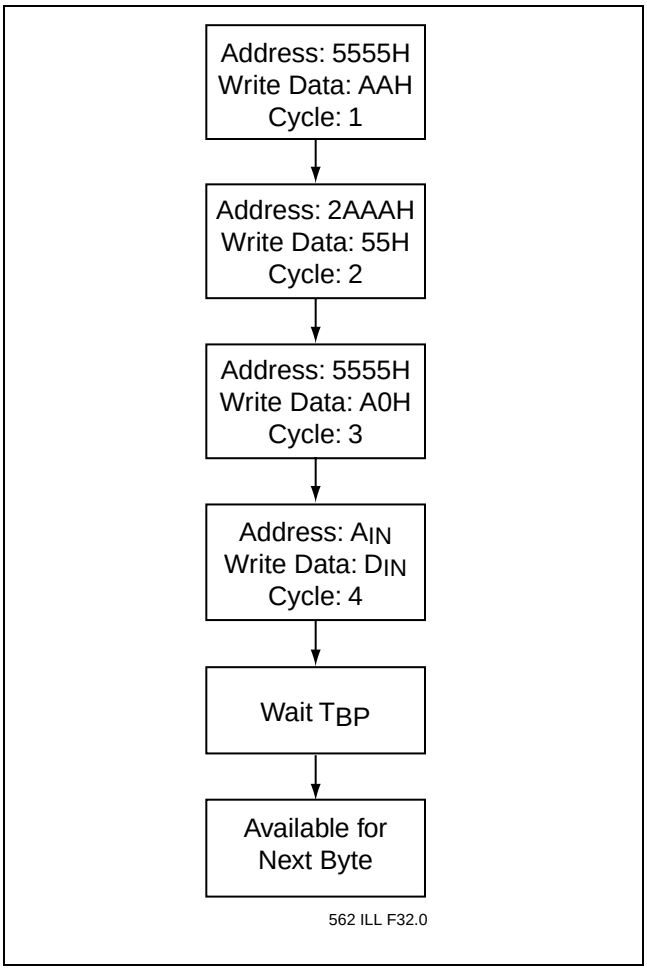


FIGURE 32: BYTE-PROGRAM ALGORITHM (LPC MODE)

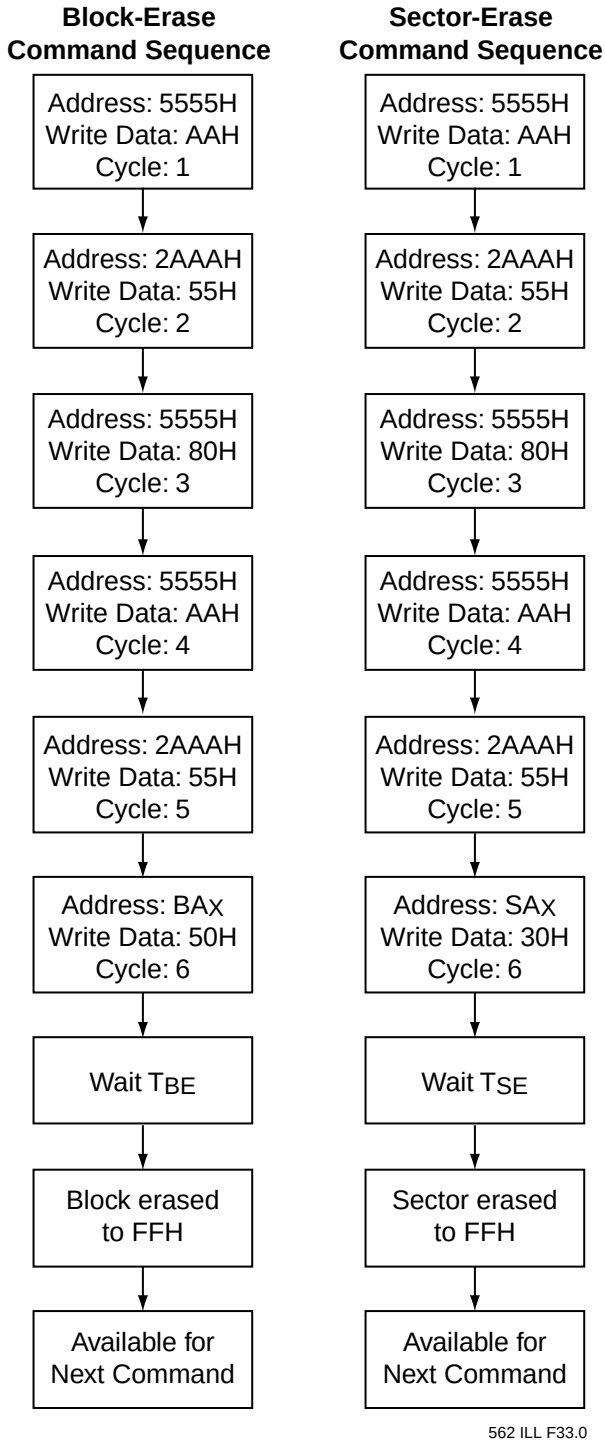


FIGURE 33: ERASE COMMAND SEQUENCES (LPC MODE)

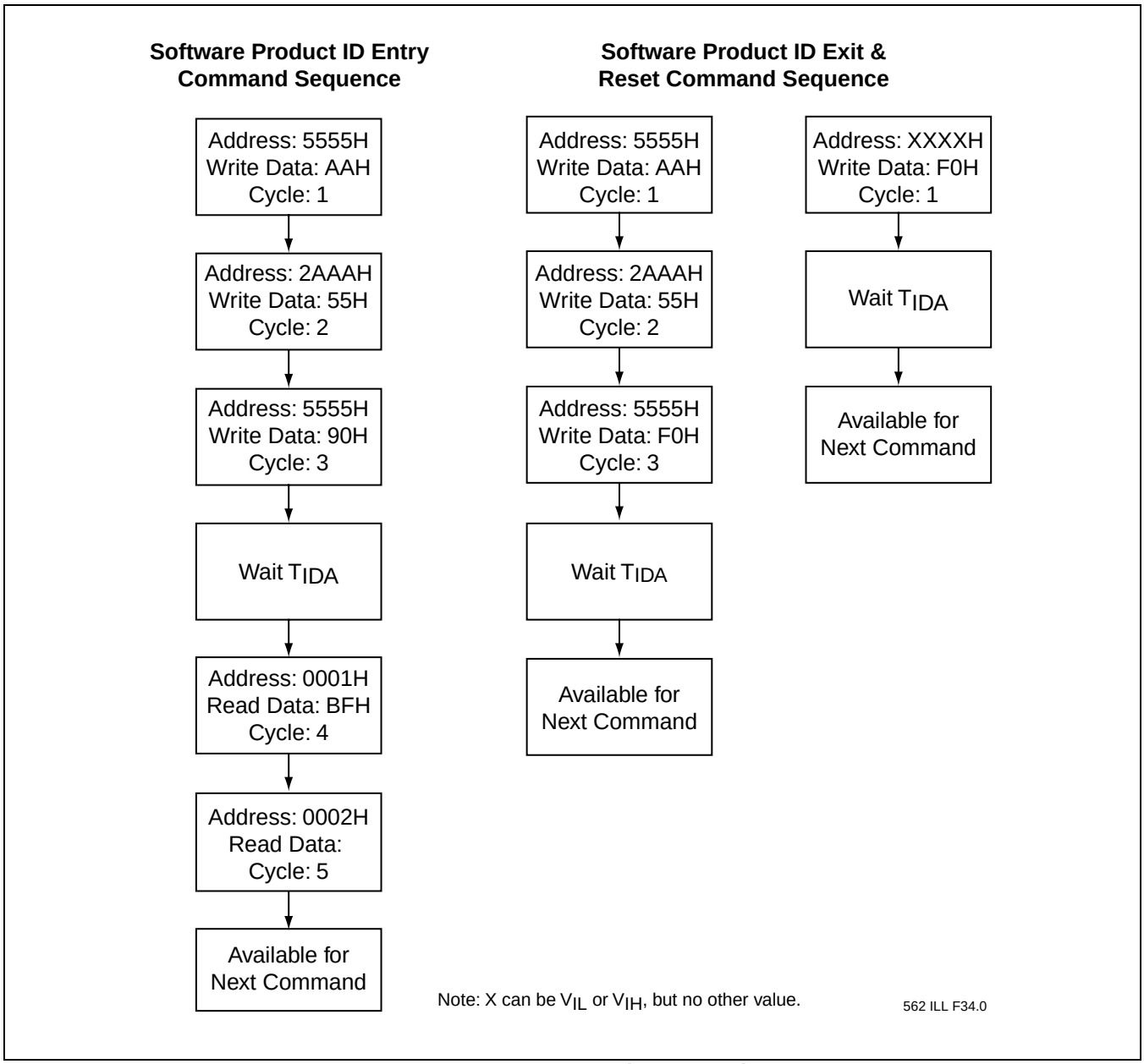


FIGURE 34: SOFTWARE PRODUCT COMMAND FLOWCHARTS (LPC MODE)

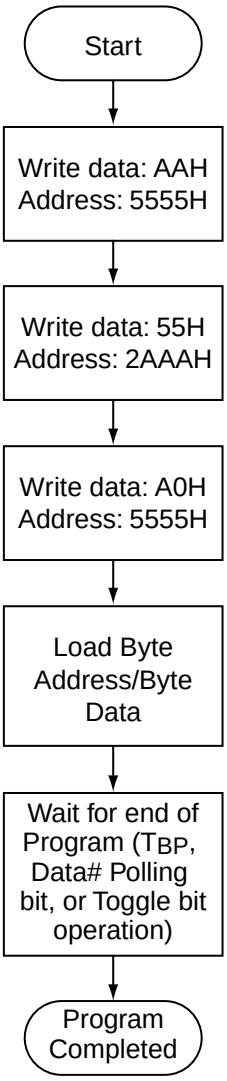


FIGURE 35: BYTE-PROGRAM ALGORITHM (PP MODE)

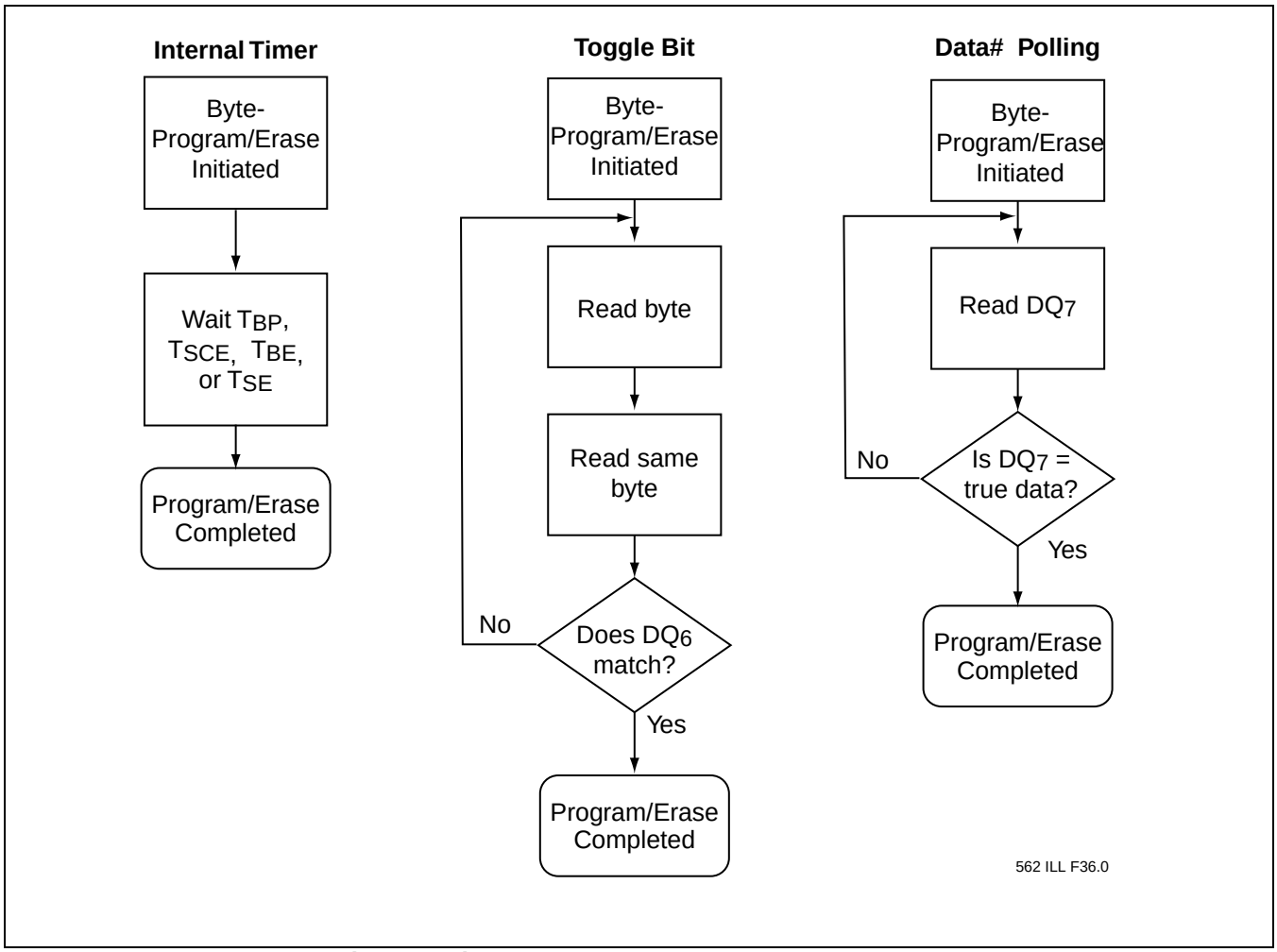


FIGURE 36: WAIT OPTIONS (PP MODE)

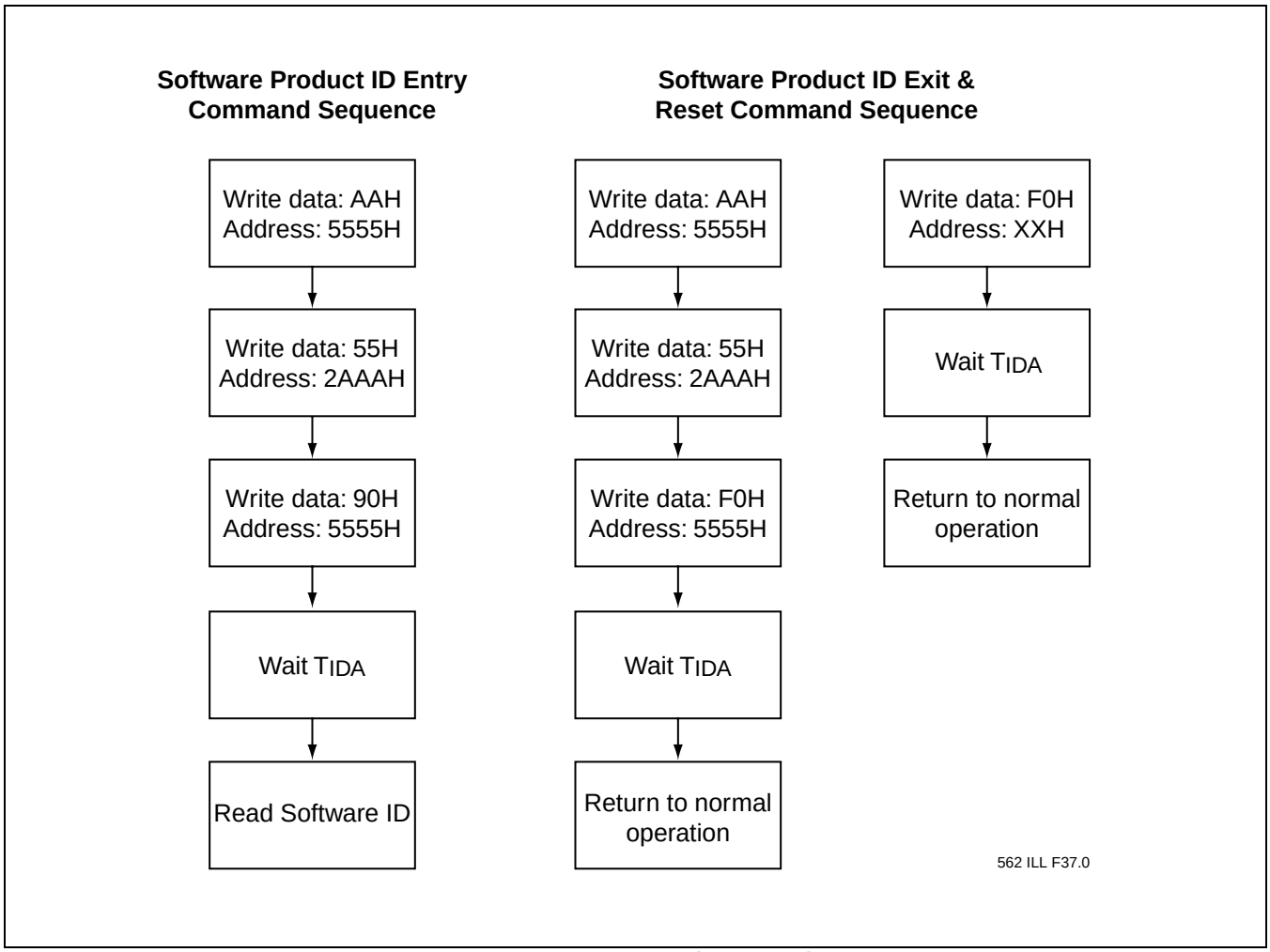


FIGURE 37: SOFTWARE PRODUCT COMMAND FLOWCHARTS (PP MODE)

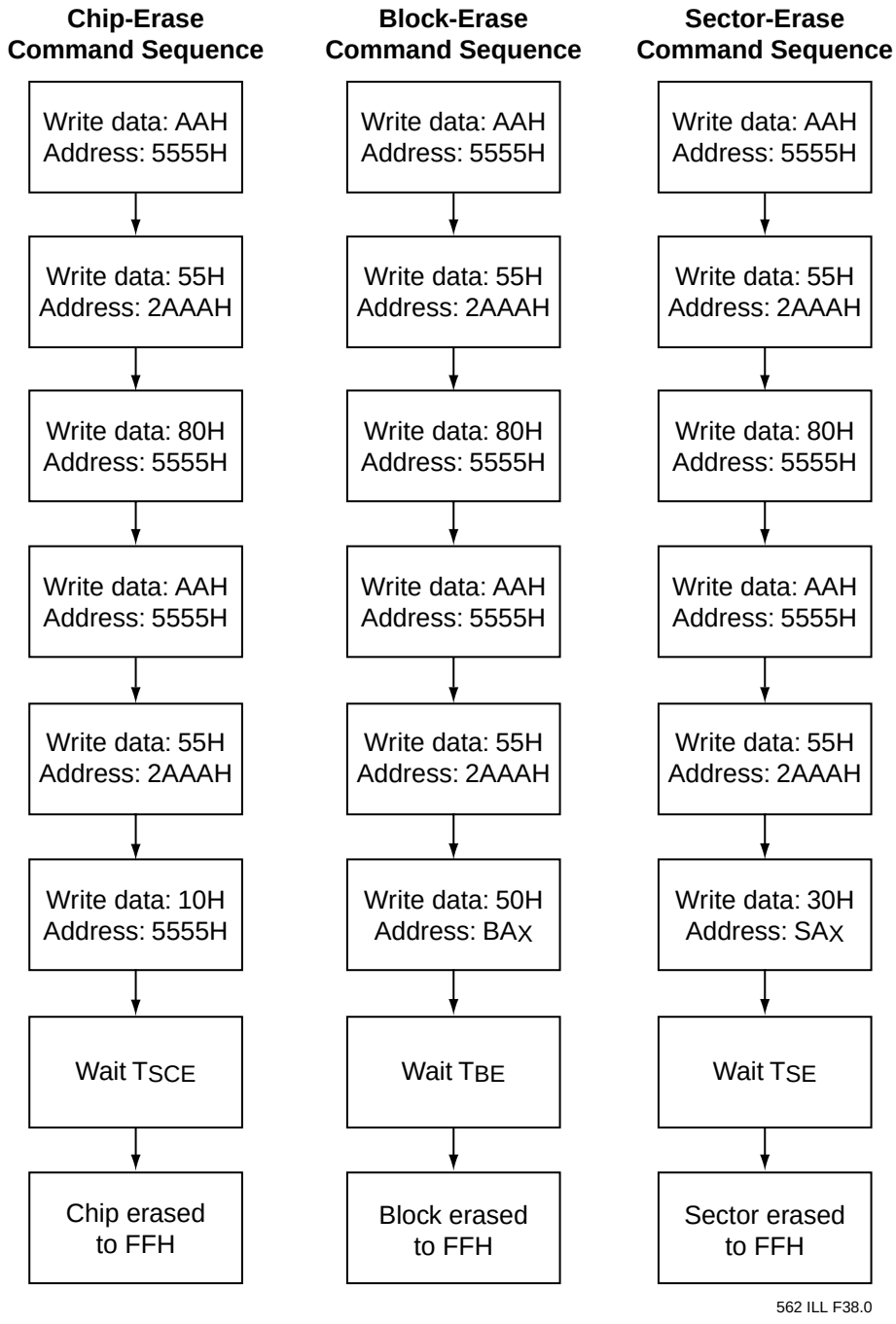
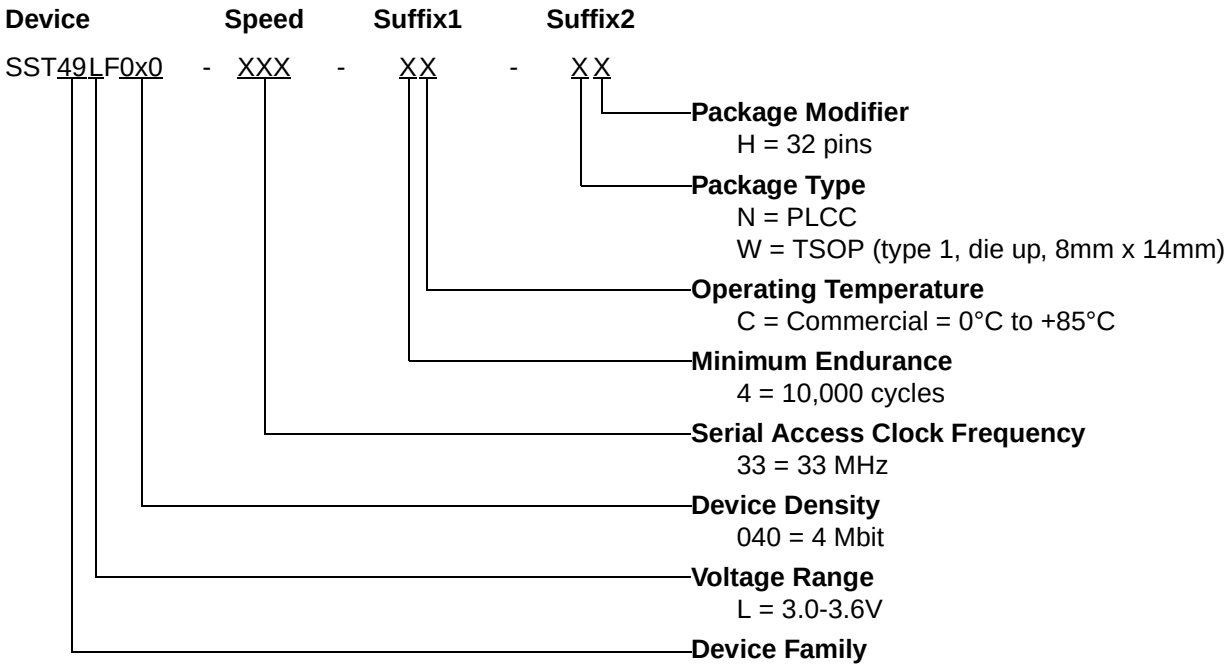


FIGURE 38: ERASE COMMAND SEQUENCE (PP MODE)

PRODUCT ORDERING INFORMATION



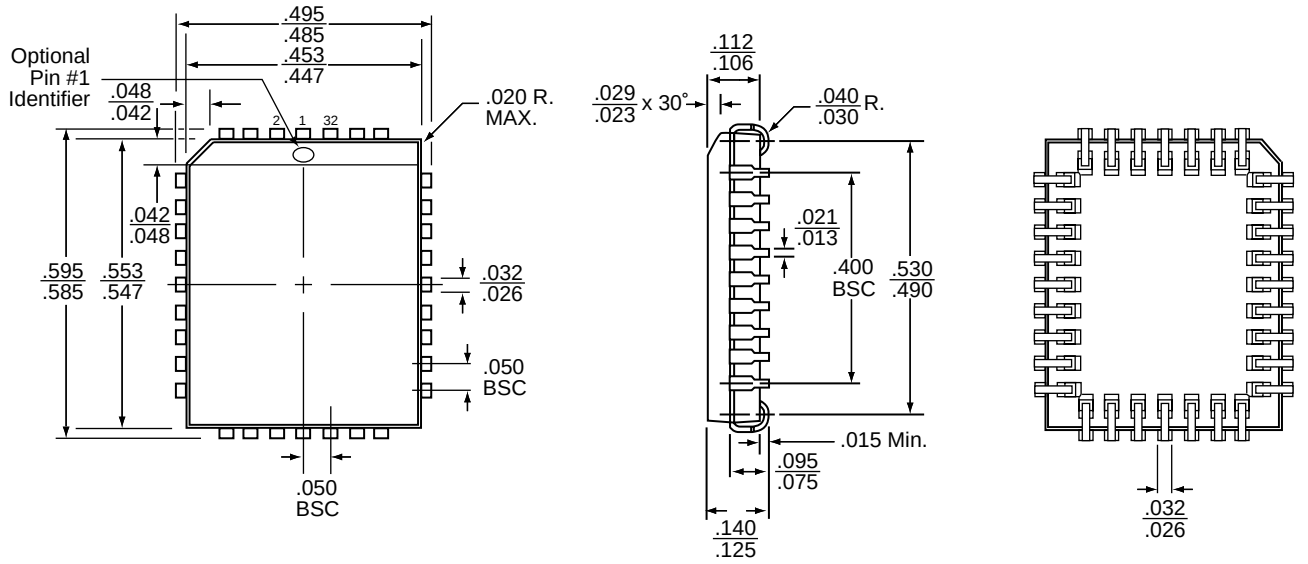
Valid combinations for SST49LF040

SST49LF040-33-4C-WH SST49LF040-33-4C-NH

Note: Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.

Advance Information

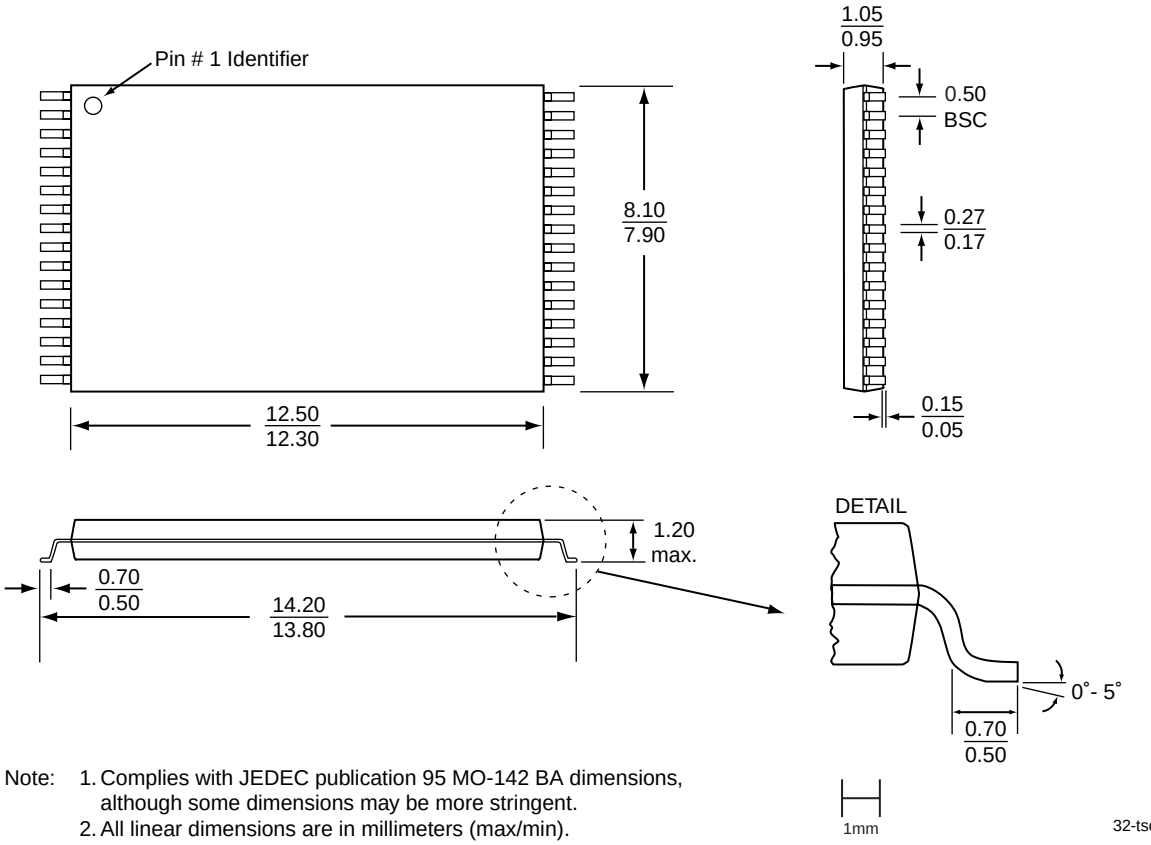
PACKAGING DIAGRAMS



Note: 1. Complies with JEDEC publication 95 MS-016 AE dimensions, although some dimensions may be more stringent.
2. All linear dimensions are in inches (max/min).
3. Dimensions do not include mold flash. Maximum allowable mold flash is .008 inches.
4. Coplanarity: 4 mils.

32-plcc-NH-3

32-LEAD PLASTIC LEAD CHIP CARRIER (PLCC)
SST PACKAGE CODE: NH



Note: 1. Complies with JEDEC publication 95 MO-142 BA dimensions, although some dimensions may be more stringent.
2. All linear dimensions are in millimeters (max/min).
3. Coplanarity: 0.1 mm
4. Maximum allowable mold flash is 0.15 mm at the package ends, and 0.25 mm between leads.

32-LEAD THIN SMALL OUTLINE PACKAGE (TSOP) 8MM X 14MM
SST PACKAGE CODE: WH